

# Mohamed Henini

## List of Publications by Year in descending order

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846  
papers

14,290  
citations

28190

55  
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43802

91  
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882  
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882  
docs citations

882  
times ranked

8135  
citing authors

#	ARTICLE	IF	CITATIONS
1	Photodegradation of organic pollutants RhB dye using UV simulated sunlight on ceria based TiO <sub>2</sub> nanomaterials for antibacterial applications. Scientific Reports, 2016, 6, 38064.	1.6	353
2	Carrier thermal escape and retrapping in self-assembled quantum dots. Physical Review B, 1999, 60, 8276-8283.	1.1	313
3	Two Dimensional Electrons in a Lateral Magnetic Superlattice. Physical Review Letters, 1995, 74, 3009-3012.	2.9	255
4	Real-time scanning Hall probe microscopy. Applied Physics Letters, 1996, 69, 1324-1326.	1.5	236
5	Paramagnetic Meissner effect in small superconductors. Nature, 1998, 396, 144-146.	13.7	232
6	Rare earth element (REE) lanthanum doped zinc oxide (La: ZnO) nanomaterials: Synthesis structural optical and antibacterial studies. Journal of Alloys and Compounds, 2017, 723, 1155-1161.	2.8	229
7	Probing the hole dispersion curves of a quantum well using resonant magnetotunneling spectroscopy. Physical Review Letters, 1991, 66, 1749-1752.	2.9	213
8	Resonant tunneling through the bound states of a single donor atom in a quantum well. Physical Review Letters, 1992, 68, 1754-1757.	2.9	213
9	Resistance Resonance Effects through Magnetic Edge States. Physical Review Letters, 2000, 84, 2231-2234.	2.9	203
10	Temperature dependence of the optical properties of InAs/AlGa self-organized quantum dots. Physical Review B, 1999, 59, 5064-5068.	1.1	202
11	Magnetic field studies of elastic scattering and optic-phonon emission in resonant-tunneling devices. Physical Review B, 1989, 39, 3438-3441.	1.1	187
12	Magnetoresistance of a two-dimensional electron gas due to a single magnetic barrier and its use for nanomagnetometry. Applied Physics Letters, 1999, 74, 2507-2509.	1.5	183
13	A one-dimensional chain state of vortex matter. Nature, 2001, 414, 728-731.	13.7	169
14	Imaging the Electron Wave Function in Self-Assembled Quantum Dots. Science, 2000, 290, 122-124.	6.0	168
15	Fermi-edge singularity in resonant tunneling. Physical Review Letters, 1994, 72, 2061-2064.	2.9	160
16	Electron-concentration-dependent quantum-well luminescence: Evidence for a negatively charged exciton. Physical Review B, 1995, 51, 7969-7972.	1.1	149
17	Spin Excitations of a Two-Dimensional Electron Gas in the Limit of Vanishing Landau Level Factor. Physical Review Letters, 1996, 77, 4604-4607.	2.9	138
18	High Temperature Gate Control of Quantum Well Spin Memory. Physical Review Letters, 2003, 91, 246601.	2.9	137

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19	Magnetoresistance of a two-dimensional electron gas in a strong periodic potential. <i>Physical Review B</i> , 1990, 42, 9229-9232.	1.1	136
20	Evaluation on La <sub>2</sub> O <sub>3</sub> garlanded ceria heterostructured binary metal oxide nanoplates for UV/ visible light induced removal of organic dye from urban wastewater. <i>South African Journal of Chemical Engineering</i> , 2018, 26, 49-60.	1.2	124
21	Coherent Terahertz Sound Amplification and Spectral Line Narrowing in a Stark Ladder Superlattice. <i>Physical Review Letters</i> , 2010, 104, 085501.	2.9	121
22	Chaotic electron diffusion through stochastic webs enhances current flow in superlattices. <i>Nature</i> , 2004, 428, 726-730.	13.7	117
23	Resonant magnetotunneling through individual self-assembled InAs quantum dots. <i>Physical Review B</i> , 1996, 54, 16401-16404.	1.1	114
24	Acoustic Phonon Emission from a Weakly Coupled Superlattice under Vertical Electron Transport: Observation of Phonon Resonance. <i>Physical Review Letters</i> , 2006, 96, 215504.	2.9	112
25	Sequential tunneling due to intersubband scattering in double-barrier resonant tunneling devices. <i>Applied Physics Letters</i> , 1988, 52, 212-214.	1.5	101
26	Observation of intrinsic bistability in resonant tunnelling devices. <i>Electronics Letters</i> , 1988, 24, 1190.	0.5	97
27	Transition metal titanium (Ti) doped LaFeO <sub>3</sub> nanoparticles for enhanced optical structural and magnetic properties. <i>Journal of Alloys and Compounds</i> , 2017, 712, 870-877.	2.8	96
28	Temperature dependence of the photoluminescence emission from thiol-capped PbS quantum dots. <i>Applied Physics Letters</i> , 2007, 90, 101913.	1.5	95
29	Probing the wave function of quantum confined states by resonant magnetotunneling. <i>Physical Review B</i> , 1993, 48, 5664-5667.	1.1	92
30	Scanning Hall probe microscopy of superconductors and magnetic materials. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1996, 14, 1202.	1.6	86
31	Electronic structure of self-assembled InAs quantum dots in GaAs matrix. <i>Applied Physics Letters</i> , 1998, 73, 1092-1094.	1.5	86
32	Probing the quantum states of self-assembled InAs dots by magnetotunneling spectroscopy. <i>Physical Review B</i> , 2002, 65, .	1.1	85
33	Photoluminescence of negatively charged excitons in high magnetic fields. <i>Physical Review B</i> , 1999, 59, 2927-2931.	1.1	84
34	Fine Structure in Magnetization of Individual Fluxoid States. <i>Physical Review Letters</i> , 2000, 85, 1528-1531.	2.9	84
35	Synthesis, structural, magnetic and optical properties of nanocrystalline ZnFe <sub>2</sub> O <sub>4</sub> . <i>Physica B: Condensed Matter</i> , 2011, 406, 1989-1994.	1.3	84
36	Electronic processes in double-barrier resonant-tunneling structures studied by photoluminescence spectroscopy in zero and finite magnetic fields. <i>Physical Review B</i> , 1990, 41, 10754-10766.	1.1	80

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37	Optical anisotropy in arrow-shaped InAs quantum dots. Physical Review B, 1998, 57, R6815-R6818.	1.1	80
38	Observation of giant magnetoresistance due to open orbits in hybrid semiconductor/ferromagnet devices. Physical Review B, 1997, 55, R16037-R16040.	1.1	79
39	Enhanced spin-relaxation time due to electron-electron scattering in semiconductor quantum wells. Physical Review B, 2007, 75, .	1.1	76
40	Enhanced magnetic properties of polymer-magnetic nanostructures synthesized by ultrasonication. Journal of Alloys and Compounds, 2017, 720, 395-400.	2.8	76
41	Observation of space-charge bulk-up and thermalisation in an asymmetric double-barrier resonant tunnelling structure. Journal of Physics Condensed Matter, 1989, 1, 10605-10611.	0.7	75
42	Photocurrent Enhancement in Hybrid Nanocrystal Quantum-Dot $p-i-n$ Photovoltaic Devices. Physical Review Letters, 2009, 102, 077402.	2.9	72
43	Charge build-up and intrinsic bistability in an asymmetric resonant-tunnelling structure. Semiconductor Science and Technology, 1988, 3, 1060-1062.	1.0	71
44	Gated resonant tunnelling devices. Electronics Letters, 1991, 27, 134.	0.5	71
45	All-optical measurement of Rashba coefficient in quantum wells. Physical Review B, 2008, 77, .	1.1	71
46	Photoluminescence spectroscopy of self-assembled InAs quantum dots in strong magnetic field and under high pressure. Applied Physics Letters, 1997, 70, 505-507.	1.5	68
47	Energy levels in self-assembled InAs/GaAs quantum dots above the pressure-induced $s$ - $p$ crossover. Physical Review B, 1998, 58, R4250-R4253.	1.1	66
48	Electrical and spectroscopic studies of space-charged buildup, energy relaxation and magnetically enhanced bistability in resonant-tunneling structures. Solid-State Electronics, 1989, 32, 1101-1108.	0.8	63
49	Role of point defects in the silicon diffusion in GaAs and Al <sub>0.3</sub> Ga <sub>0.7</sub> As and in the related superlattice disordering. Journal of Applied Physics, 1992, 71, 2225-2237.	1.1	62
50	The oscillatory magnetoresistance of electrons in a square superlattice potential. Journal of Physics Condensed Matter, 1989, 1, 8257-8262.	0.7	60
51	Measuring the Probability Density of Quantum Confined States. Physical Review Letters, 1995, 75, 1996-1999.	2.9	60
52	Cyclotron resonance in ultra-low-hole-density narrow p-type GaAs/(Al,Ga)As quantum wells. Physical Review B, 1997, 55, 2503-2511.	1.1	60
53	Direct Observation of Melting of the Vortex Solid in Bi <sub>2</sub> Sr <sub>2</sub> CaCu <sub>2</sub> O <sub>8</sub> + $\delta$ Single Crystals. Physical Review Letters, 1998, 80, 3610-3613.	2.9	58
54	Observation of spin splitting in single InAs self-assembled quantum dots in AlAs. Applied Physics Letters, 1998, 73, 354-356.	1.5	57

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55	Temperature dependence of large positive magnetoresistance in hybrid ferromagnetic/semiconductor devices. Applied Physics Letters, 1998, 72, 1724-1726.	1.5	55
56	Carrier localization in GaBiAs probed by photomodulated transmittance and photoluminescence. Journal of Applied Physics, 2009, 106, 023518.	1.1	55
57	Interface Induced Uniaxial Magnetic Anisotropy in Amorphous CoFeB Films on AlGaAs(001). Physical Review Letters, 2008, 100, 117201.	2.9	54
58	Current bistability in double-barrier resonant-tunneling devices. Physical Review B, 1989, 39, 6205-6207.	1.1	53
59	Influence of reaction time and synthesis temperature on the physical properties of ZnO nanoparticles synthesized by the hydrothermal method. Applied Physics A: Materials Science and Processing, 2018, 124, 1.	1.1	53
60	Molecular beam epitaxy of GaBiAs on (311)B GaAs substrates. Applied Physics Letters, 2007, 91, 251909.	1.5	50
61	Landau-Level Spectroscopy of a Two-Dimensional Electron System by Tunneling through a Quantum Dot. Physical Review Letters, 2000, 84, 729-732.	2.9	49
62	Oscillatory Dyakonov-Perel spin dynamics in two-dimensional electron gases. Physical Review B, 2007, 76, .	1.1	49
63	Phonon Absorption at the Magnetoroton Minimum in the Fractional Quantum Hall Effect. Physical Review Letters, 1995, 74, 2339-2342.	2.9	47
64	Influence of the As overpressure during the molecular beam epitaxy growth of Si-doped (211)A and (311)A GaAs. Applied Physics Letters, 1995, 66, 2846-2848.	1.5	47
65	Self-sustained current oscillation above 100 GHz in a GaAs/AlAs superlattice. Applied Physics Letters, 1999, 74, 2179-2181.	1.5	47
66	Thermal effects in quantum dot lasers. Journal of Applied Physics, 1999, 85, 625-627.	1.1	47
67	Spin-orbit fields in asymmetric (001)-oriented GaAs/Al quantum wells. Physical Review B, 2011, 83, .	1.1	47
68	Optical properties and device applications of (InGa)As self-assembled quantum dots grown on (311)B GaAs substrates. Applied Physics Letters, 1998, 73, 1415-1417.	1.5	46
69	Structural and optical characterization of self-assembled InAs-GaAs quantum dots grown on high index surfaces. Microelectronics Journal, 1997, 28, 933-938.	1.1	45
70	Piezoelectric effects in In <sub>0.5</sub> Ga <sub>0.5</sub> As self-assembled quantum dots grown on (311)B GaAs substrates. Applied Physics Letters, 2000, 77, 2979-2981.	1.5	45
71	Excitation mechanisms of photoluminescence in double-barrier resonant-tunneling structures. Physical Review B, 1990, 42, 3069-3076.	1.1	44
72	Nonradiative exciton energy transfer in hybrid organic-inorganic heterostructures. Physical Review B, 2008, 77, .	1.1	44

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73	Thermopower measurements of the coupling of phonons to electrons and composite fermions. Physical Review B, 1998, 58, 2017-2025.	1.1	43
74	High-temperature light emission from InAs quantum dots. Applied Physics Letters, 1999, 75, 814-816.	1.5	42
75	Hall anomaly of diffusive magnetic waveguides. Physical Review B, 2003, 67, .	1.1	42
76	Piezoelectric-induced quantum-confined Stark effect in self-assembled InAs quantum dots grown on (N11) GaAs substrates. Applied Physics Letters, 2000, 77, 1982-1984.	1.5	41
77	Improvement of the nutritional quality of foods as a public health tool. Public Health, 2011, 125, 717-724.	1.4	41
78	Effect of As overpressure on Si-doped (111)A GaAs grown by molecular beam epitaxy: a photoluminescence study. Semiconductor Science and Technology, 1992, 7, 1504-1507.	1.0	40
79	D <sup>+</sup> centers probed by resonant tunneling spectroscopy. Physical Review B, 1996, 53, 9554-9557.	1.1	40
80	Even-Denominator Filling Factors in the Thermoelectric Power of a Two-Dimensional Electron Gas. Physical Review Letters, 1996, 76, 3630-3633.	2.9	40
81	Stark shift in electroluminescence of individual InAs quantum dots. Applied Physics Letters, 2000, 76, 3932-3934.	1.5	39
82	Magnetoresistance oscillations due to internal Landau band structure of a two-dimensional electron system in a periodic magnetic field. Physical Review B, 2001, 64, .	1.1	38
83	Terahertz phonon optics in GaAs/AlAs superlattice structures. Physical Review B, 2003, 68, .	1.1	38
84	Distribution of bismuth atoms in epitaxial GaAsBi. Applied Physics Letters, 2011, 98, 101902.	1.5	38
85	Imaging nonequilibrium phonon-induced backscattering in the quantum Hall regime. Physical Review Letters, 1992, 69, 1684-1686.	2.9	37
86	Quantum Hall ferromagnet at high filling factors: A magnetic-field-induced Stoner transition. Physical Review B, 2005, 72, .	1.1	37
87	Resonant Magnetotunneling via One-Dimensional Quantum Confined States. Physical Review Letters, 1994, 73, 1146-1149.	2.9	36
88	Carrier thermalization within a disordered ensemble of self-assembled quantum dots. Physical Review B, 2000, 62, 11084-11088.	1.1	36
89	Tailoring the electronic properties of GaAs/AlAs superlattices by InAs layer insertions. Applied Physics Letters, 2002, 81, 661-663.	1.5	36
90	Strain relaxation in stacked InAs/GaAs quantum dots studied by Raman scattering. Applied Physics Letters, 2003, 83, 3069-3071.	1.5	36

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91	Properties and applications of quantum dot heterostructures grown by molecular beam epitaxy. <i>Nanoscale Research Letters</i> , 2006, 1, 32-45.	3.1	36
92	Growth and electrical transport properties of very high mobility two-dimensional hole gases displaying persistent photoconductivity. <i>Applied Physics Letters</i> , 1994, 65, 2054-2056.	1.5	35
93	Terahertz response of zero-dimensional states in resonant tunneling diodes. <i>Applied Physics Letters</i> , 1995, 67, 3453-3455.	1.5	35
94	Magnetophotoluminescence of negatively charged excitons in narrow quantum wells. <i>Physical Review B</i> , 2001, 63, .	1.1	35
95	Submicrometer resonant tunnelling diodes fabricated by photolithography and selective wet etching. <i>Applied Physics Letters</i> , 1994, 65, 1124-1126.	1.5	34
96	Quantum-dot phonons in self-assembled InAs/GaAs quantum dots: Dependence on the coverage thickness. <i>Applied Physics Letters</i> , 2000, 77, 3556-3558.	1.5	34
97	Generation and propagation of monochromatic acoustic phonons in gallium arsenide. <i>Applied Physics Letters</i> , 2002, 81, 3497-3499.	1.5	34
98	Radioluminescence and photoluminescence characterization of Eu and Tb doped barium stannate phosphor ceramics. <i>Journal of Alloys and Compounds</i> , 2014, 590, 417-423.	2.8	34
99	Fabrication of novel transparent Co <sub>3</sub> O <sub>4</sub> -TiO <sub>2</sub> nanowires p-n heterojunction diodes for multiband photodetection applications. <i>Journal of Alloys and Compounds</i> , 2017, 712, 7-14.	2.8	34
100	Magnetoresistance and Hall magnetometry of single submicron ferromagnetic structures. <i>Journal of Applied Physics</i> , 2000, 87, 5986-5988.	1.1	33
101	Integrated piezoresistive sensors for atomic force-guided scanning Hall probe microscopy. <i>Applied Physics Letters</i> , 2003, 82, 3538-3540.	1.5	33
102	Temperature dependence of the breakdown of the quantum Hall effect studied by induced currents. <i>Physical Review B</i> , 2004, 70, .	1.1	33
103	Nitrogen incorporation into strained (In, Ga) (As, N) thin films grown on (100), (511), (411), (311), and (111) GaAs substrates studied by photoreflectance spectroscopy and high-resolution x-ray diffraction. <i>Journal of Applied Physics</i> , 2006, 100, 093522.	1.1	33
104	Subterahertz Acoustical Pumping of Electronic Charge in a Resonant Tunneling Device. <i>Physical Review Letters</i> , 2012, 108, 226601.	2.9	33
105	Surface effects of vapour-liquid-solid driven Bi surface droplets formed during molecular-beam-epitaxy of GaAsBi. <i>Scientific Reports</i> , 2016, 6, 28860.	1.6	33
106	From Khoi-San indigenous knowledge to bioengineered CeO <sub>2</sub> nanocrystals to exceptional UV-blocking green nanocosmetics. <i>Scientific Reports</i> , 2022, 12, 3468.	1.6	33
107	Adsorbed and substituted Sb dimers on GaAs(001). <i>Physical Review B</i> , 1996, 53, R16148-R16151.	1.1	32
108	Controlling the shape of InAs self-assembled quantum dots by thin GaAs capping layers. <i>Journal of Crystal Growth</i> , 2003, 251, 155-160.	0.7	32

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109	Resistance Noise Scaling in a Dilute Two-Dimensional Hole System in GaAs. <i>Physical Review Letters</i> , 2003, 90, 076402.	2.9	32
110	Scanning capacitance imaging of compressible and incompressible quantum Hall effect edge strips. <i>New Journal of Physics</i> , 2012, 14, 083015.	1.2	31
111	Solid state synthesis of SrAl <sub>2</sub> O <sub>4</sub> :Mn <sup>2+</sup> co-doped with Nd <sup>3+</sup> phosphor and its optical properties. <i>Journal of Luminescence</i> , 2013, 144, 128-132.	1.5	31
112	Band gap and partial density of states for ZnO: Under high pressure. <i>Journal of Alloys and Compounds</i> , 2015, 619, 812-819.	2.8	31
113	Hall Photovoltage Imaging of the Edge of a Quantum Hall Device. <i>Physical Review Letters</i> , 1997, 79, 5114-5117.	2.9	30
114	Fundamental Relation between Electrical and Thermoelectric Transport Coefficients in the Quantum Hall Regime. <i>Physical Review Letters</i> , 1997, 78, 4621-4624.	2.9	30
115	InAs quantum dots grown on nonconventionally oriented GaAs substrates. <i>Journal of Crystal Growth</i> , 1998, 187, 126-132.	0.7	30
116	Multiple gated InAs dot ensembles. <i>Applied Physics Letters</i> , 1999, 75, 671-673.	1.5	30
117	Hybrid magneto-electric states in resonant tunnelling structures. <i>Superlattices and Microstructures</i> , 1989, 5, 527-530.	1.4	29
118	Zero-dimensional states in macroscopic resonant tunneling devices. <i>Applied Physics Letters</i> , 1994, 64, 2563-2565.	1.5	29
119	Spectral analysis of InGaAs/GaAs quantum-dot lasers. <i>Applied Physics Letters</i> , 1999, 75, 2169-2171.	1.5	29
120	Advances in self-assembled semiconductor quantum dot lasers. <i>Microelectronics Journal</i> , 2005, 36, 950-956.	1.1	29
121	Ultrafast Strain-Induced Current in a GaAs Schottky Diode. <i>Physical Review Letters</i> , 2011, 106, 066602.	2.9	29
122	Revealing the nature of low-temperature photoluminescence peaks by laser treatment in van der Waals epitaxially grown WS <sub>2</sub> monolayers. <i>Nanoscale</i> , 2018, 10, 4807-4815.	2.8	29
123	Zn diffusion-induced disorder in AlAs/GaAs superlattices. <i>Semiconductor Science and Technology</i> , 1989, 4, 841-846.	1.0	28
124	Surface acoustic wave attenuation by localized electrons in a 2DEG at a GaAs/AlGaAs heterojunction. <i>Semiconductor Science and Technology</i> , 1992, 7, 641-647.	1.0	28
125	Edge channels and the quantum-Hall-effect breakdown. <i>Physical Review B</i> , 1994, 49, 5379-5385.	1.1	28
126	Energy states of Be in GaAs. <i>Physical Review B</i> , 1996, 53, 12829-12834.	1.1	28



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127	Indium interdiffusion in annealed and implanted InAs/(AlGa)As self-assembled quantum dots. Journal of Applied Physics, 2001, 89, 6044-6047.	1.1	28
128	Evidence for sequential tunnelling and charge build-up in double barrier resonant tunnelling devices. Surface Science, 1988, 196, 404-409.	0.8	27
129	Annealing effects on Si-doped GaAs grown on high-index planes by molecular-beam epitaxy. Journal of Applied Physics, 1994, 75, 3151-3157.	1.1	27
130	Dynamic quantum-confined stark effect in self-assembled InAs quantum dots. Applied Physics Letters, 2001, 78, 931-933.	1.5	27
131	The resistance of two quantum point contacts in series. Journal of Physics Condensed Matter, 1989, 1, 7505-7511.	0.7	26
132	Electroluminescence investigations of electron and hole resonant tunneling in p-i-n double-barrier structures. Physical Review B, 1992, 45, 9513-9516.	1.1	26
133	$(2\text{Å}-4)/c(2\text{Å}-8)$ to $(4\text{Å}-2)/c(8\text{Å}-2)$ transition on GaAs(001) surfaces. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1996, 14, 943.	1.6	26
134	Influence of high-index GaAs substrates on the growth of highly strained (InGa)As/GaAs heterostructures. Journal of Crystal Growth, 1999, 201-202, 276-279.	0.7	26
135	Micromachined III-V cantilevers for AFM-tracking scanning Hall probe microscopy. Journal of Micromechanics and Microengineering, 2003, 13, 124-128.	1.5	26
136	Thermal quenching of single localized excitons in GaInNAs layers. Applied Physics Letters, 2011, 98, .	1.5	26
137	Luminescence characterization of cerium doped yttrium gadolinium aluminate phosphors. Optical Materials, 2012, 34, 1921-1925.	1.7	26
138	A comprehensive study on the effects of gamma radiation on the physical properties of a two-dimensional WS <sub>2</sub> monolayer semiconductor. Nanoscale Horizons, 2020, 5, 259-267.	4.1	26
139	Resonant tunnelling studies of magnetoelectric quantisation in wide quantum wells. Journal of Physics Condensed Matter, 1989, 1, 4865-4871.	0.7	25
140	Edge effects in a gated submicron resonant tunneling diode. Applied Physics Letters, 1992, 60, 2508-2510.	1.5	25
141	Phonoconductivity measurement of the phonon absorption by a two-dimensional hole gas in a GaAs heterojunction. Physical Review B, 1996, 54, 2019-2027.	1.1	25
142	Rashba spin-splitting of electrons in asymmetric quantum wells. Physical Review B, 2010, 82, .	1.1	25
143	Raman scattering by the E <sub>2h</sub> and A <sub>1</sub> (LO) phonons of In <sub>x</sub> Ga <sub>1-x</sub> N epilayers (0.25 < x < 0.75) grown by molecular beam epitaxy. Journal of Applied Physics, 2012, 111, 063502.	1.1	25
144	Probing the anisotropic dispersion of hole states in (100) and (311)A AlAs/GaAs/AlAs quantum wells. Semiconductor Science and Technology, 1994, 9, 298-309.	1.0	24

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145	Absence of long-range ordered reconstruction on the GaAs(311)A surface. <i>Physical Review B</i> , 1997, 55, 15397-15400.	1.1	24
146	Suppression of electron channelling in microscopic magnetic waveguides. <i>Physical Review B</i> , 2001, 64, .	1.1	24
147	Electrical rectification by magnetic edge states. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2002, 13, 699-702.	1.3	24
148	Generation and detection of terahertz coherent transverse-polarized acoustic phonons by ultrafast optical excitation of GaAs $\wedge$ AlAs superlattices. <i>Applied Physics Letters</i> , 2006, 88, 134112.	1.5	24
149	Surface-Enhanced Raman Spectroscopy Study of 4-ATP on Gold Nanoparticles for Basal Cell Carcinoma Fingerprint Detection. <i>Journal of Electronic Materials</i> , 2016, 45, 2563-2568.	1.0	24
150	Hole space charge buildup and evidence for sequential tunneling in p $\wedge$ -type double barrier resonant tunneling devices. <i>Applied Physics Letters</i> , 1992, 60, 1474-1476.	1.5	23
151	Evidence for quantum states corresponding to families of stable and chaotic classical orbits in a wide potential well. <i>Physical Review B</i> , 1995, 51, 18029-18032.	1.1	23
152	Energy relaxation by photoexcited carriers in the InAs/GaAs quantum-dot system: Bolometric detection of strong acoustic-phonon emission. <i>Applied Physics Letters</i> , 1999, 75, 3832-3834.	1.5	23
153	Time-resolved photoluminescence of InAs quantum dots in a GaAs quantum well. <i>Applied Physics Letters</i> , 2004, 84, 3046-3048.	1.5	23
154	Electric-field inversion asymmetry: Rashba and Stark effects for holes in resonant tunneling devices. <i>Physical Review B</i> , 2006, 74, .	1.1	23
155	Efficient light harvesting in hybrid CdTe nanocrystal/bulk GaAs p-i-n photovoltaic devices. <i>Applied Physics Letters</i> , 2009, 94, .	1.5	23
156	Raman scattering reveals strong LO-phonon-hole-plasmon coupling in nominally undoped GaAsBi: optical determination of carrier concentration. <i>Optics Express</i> , 2014, 22, 11680.	1.7	23
157	Characterisation of temperature dependent parameters of multi-quantum well (MQW) Ti/Au/n-AlGaAs/n-GaAs/n-AlGaAs Schottky diodes. <i>Superlattices and Microstructures</i> , 2017, 111, 1010-1021.	1.4	23
158	Observation of the transition to an insulating state consistent with a Wigner solid in a high-density 2D hole gas. <i>Physica B: Condensed Matter</i> , 1993, 184, 95-99.	1.3	22
159	Edge phonoconductivity in a magnetically quantized two-dimensional electron gas. <i>Physical Review B</i> , 1994, 49, 2585-2594.	1.1	22
160	Upconversion electroluminescence in InAs quantum dot light-emitting diodes. <i>Applied Physics Letters</i> , 2008, 92, .	1.5	22
161	Raman scattering studies of strain effects in (100) and (311)B GaAs $\wedge$ xBix epitaxial layers. <i>Journal of Applied Physics</i> , 2013, 114, 193516.	1.1	22
162	Visible to infrared low temperature luminescence of Er <sup>3+</sup> , Nd <sup>3+</sup> and Sm <sup>3+</sup> in CaSnO <sub>3</sub> phosphors. <i>Applied Radiation and Isotopes</i> , 2015, 99, 69-76.	0.7	22

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163	Quantum-resolved investigations of flux dynamics: Collective and single vortex effects. <i>Physical Review Letters</i> , 1993, 71, 3854-3857.	2.9	21
164	Resonant tunneling and photoluminescence spectroscopy in quantum wells containing self-assembled quantum dots. <i>Journal of Applied Physics</i> , 2000, 88, 2005-2012.	1.1	21
165	Study of electron-hole generation and recombination in semiconductors using the Osaka free electron laser. <i>Physica B: Condensed Matter</i> , 2002, 314, 431-436.	1.3	21
166	Voltage-controlled hole spin injection in nonmagnetic GaAs/AlAs resonant tunneling structures. <i>Physical Review B</i> , 2006, 73, .	1.1	21
167	Numerical simulation of bias and photo stress on indium gallium zinc-oxide thin film transistors. <i>Vacuum</i> , 2015, 120, 59-67.	1.6	21
168	Cyclotron resonance of high-mobility GaAs/AlGaAs (311) 2DHGs. <i>Semiconductor Science and Technology</i> , 1993, 8, 1465-1469.	1.0	20
169	Resonant tunnelling at far infra-red frequencies. <i>Journal of Physics Condensed Matter</i> , 1994, 6, 3945-3954.	0.7	20
170	Disorder-driven intermediate state in the lattice melting transition of Bi <sub>2</sub> Sr <sub>2</sub> CaCu <sub>2</sub> O <sub>8</sub> + $\delta$ single crystals. <i>Physical Review B</i> , 1997, 56, R14295-R14298.	1.1	20
171	Scanning Hall probe microscopy of ferromagnetic structures. <i>Journal of Magnetism and Magnetic Materials</i> , 1999, 196-197, 917-919.	1.0	20
172	Nonlinear charging effect of quantum dots in a p <sup>+</sup> -i <sup>+</sup> -n diode. <i>Physical Review B</i> , 2003, 68, .	1.1	20
173	Magnetoanisotropy of electron-correlation-enhanced tunneling through a quantum dot. <i>Physical Review B</i> , 2007, 75, .	1.1	20
174	Structural and optical properties of dilute InAsN grown by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2010, 108, .	1.1	20
175	Unusual broadening of E <sub>0</sub> and E <sub>0</sub> + $\hbar$ $\omega$ SO transitions in GaAsBi studied by electromodulation spectroscopy. <i>Journal of Applied Physics</i> , 2012, 111, 066103.	1.1	20
176	SiC polytypes and doping nature effects on electrical properties of ZnO-SiC Schottky diodes. <i>Microelectronic Engineering</i> , 2017, 171, 11-19.	1.1	20
177	TLM modelling of the thermal behaviour of conducting films on insulating substrates. <i>Journal Physics D: Applied Physics</i> , 1987, 20, 1445-1450.	1.3	19
178	Inverted bistability in the current-voltage characteristics of a resonant tunneling device. <i>Solid-State Electronics</i> , 1989, 32, 1467-1471.	0.8	19
179	Collective cyclotron modes in high-mobility two-dimensional hole systems in GaAs - (Ga, Al)As heterojunctions: I. Experiments at low magnetic fields and theory. <i>Journal of Physics Condensed Matter</i> , 1997, 9, 3163-3179.	0.7	19
180	Intersubband relaxation lifetimes in p-GaAs/AlGaAs quantum wells below the LO-phonon energy measured in a free electron laser experiment. <i>Semiconductor Science and Technology</i> , 1999, 14, L25-L28.	1.0	19

#	ARTICLE	IF	CITATIONS
181	Trion formation in narrow GaAs quantum well structures. <i>Physical Review B</i> , 2005, 71, .	1.1	19
182	Raman scattering in InAs/(AlGa)As self-assembled quantum dots: Evidence of Al intermixing. <i>Applied Physics Letters</i> , 2006, 88, 141905.	1.5	19
183	Probing the intermixing in In(Ga)As/GaAs self-assembled quantum dots by Raman scattering. <i>Journal of Applied Physics</i> , 2006, 99, 043501.	1.1	19
184	Correlations between the band structure, activation energies of electron traps, and photoluminescence in n-type GaNAs layers. <i>Applied Physics Letters</i> , 2012, 101, 082109.	1.5	19
185	Structural, electronic and vibrational properties of InN under high pressure. <i>Physica B: Condensed Matter</i> , 2012, 407, 1008-1013.	1.3	19
186	Thermal annealing effects on the optical and structural properties of (100) GaAs <sub>1-x</sub> Bix layers grown by Molecular Beam Epitaxy. <i>Superlattices and Microstructures</i> , 2014, 65, 48-55.	1.4	19
187	Orientation dependence of the Si doping of GaAs grown by molecular beam epitaxy. <i>Semiconductor Science and Technology</i> , 1993, 8, 167-171.	1.0	18
188	Modulation of the luminescence spectra of InAs self-assembled quantum dots by resonant tunneling through a quantum well. <i>Physical Review B</i> , 2000, 62, 13595-13598.	1.1	18
189	Pulsed magnetic fields as a probe of self-assembled semiconductor nanostructures. <i>Physica B: Condensed Matter</i> , 2004, 346-347, 421-427.	1.3	18
190	Modeling the effect of 1MeV electron irradiation on the performance of n+ $\mu$ -p+ silicon space solar cells. <i>Radiation Physics and Chemistry</i> , 2016, 123, 103-108.	1.4	18
191	Investigation of optical and electrical properties of erbium-doped TiO <sub>2</sub> thin films for photodetector applications. <i>Journal of Materials Science: Materials in Electronics</i> , 2018, 29, 19588-19600.	1.1	18
192	Luminescent MoS <sub>2</sub> Quantum Dots with Tunable Operating Potential for Energy-Enhanced Aqueous Supercapacitors. <i>ACS Omega</i> , 2021, 6, 4542-4550.	1.6	18
193	Deep states in GaAs LEC crystals. <i>Solid-State Electronics</i> , 1986, 29, 483-488.	0.8	17
194	Magnetophonon resonance effects in the phonon emission by a hot two-dimensional electron gas in a GaAs-AlGaAs heterojunction. <i>Journal of Physics Condensed Matter</i> , 1989, 1, 1153-1158.	0.7	17
195	Noise model for double barrier resonant tunnel diodes. <i>Electronics Letters</i> , 1991, 27, 2158.	0.5	17
196	Molecular beam epitaxy growth of GaAs/AlAs double-barrier resonant tunnelling devices on (311)A substrates. <i>Semiconductor Science and Technology</i> , 1992, 7, 267-270.	1.0	17
197	Investigating the cubic anisotropy of the confined hole subbands of an AlAs/GaAs/AlAs quantum well using resonant magnetotunneling spectroscopy. <i>Applied Physics Letters</i> , 1992, 61, 84-86.	1.5	17
198	Nonequilibrium Acoustic Phonon-Assisted Tunneling in GaAs/(AlGa)As Double Barrier Devices. <i>Physical Review Letters</i> , 1995, 75, 308-311.	2.9	17

#	ARTICLE	IF	CITATIONS
199	Effect of As overpressure on Si-doped (111)A, (211)A and (311)A GaAs grown by molecular beam epitaxy. <i>Microelectronics Journal</i> , 1995, 26, 759-765.	1.1	17
200	Magnetic-field-induced resonant tunneling in parallel two-dimensional systems. <i>Physical Review B</i> , 1996, 54, R2315-R2318.	1.1	17
201	Magnetic-field dependence of the spin states of the negatively charged exciton in GaAs quantum wells. <i>Physical Review B</i> , 2002, 65, .	1.1	17
202	Optical control of spins in semiconductors. <i>Journal Physics D: Applied Physics</i> , 2003, 36, 2198-2203.	1.3	17
203	Circular polarization from a nonmagnetic p-i-n resonant tunneling diode. <i>Applied Physics Letters</i> , 2007, 90, 062120.	1.5	17
204	The role of optical rectification in the generation of terahertz radiation from GaBiAs. <i>Applied Physics Letters</i> , 2009, 94, .	1.5	17
205	Effect of growth techniques on the structural, optical and electrical properties of indium doped TiO <sub>2</sub> thin films. <i>Journal of Alloys and Compounds</i> , 2018, 766, 194-203.	2.8	17
206	Effect of indium doping on the electrical and structural properties of TiO <sub>2</sub> thin films used in MOS devices. <i>Journal of Alloys and Compounds</i> , 2019, 775, 202-213.	2.8	17
207	Ballistic transport in resonant tunnelling devices with wide quantum wells. <i>Journal of Physics Condensed Matter</i> , 1989, 1, 3025-3030.	0.7	16
208	The effect of the X conduction band minima on resonant tunnelling and charge build-up in double barrier structures based on n-GaAs/(AlGa)As. <i>Solid-State Electronics</i> , 1989, 32, 1731-1735.	0.8	16
209	Optical investigation of charge accumulation and bistability in an asymmetric double barrier resonant tunneling heterostructure. <i>Surface Science</i> , 1990, 228, 373-377.	0.8	16
210	Anisotropy of the confined hole states in a (311)AAlAs/GaAs/AlAs quantum-well system: Evidence for a camelâ€™s-back band structure. <i>Physical Review B</i> , 1992, 46, 15586-15589.	1.1	16
211	X-valley-related donor states and resonant tunneling in a single-barrier diode. <i>Physical Review B</i> , 1998, 57, 7214-7218.	1.1	16
212	Polarization resolved luminescence in asymmetric n-type GaAs <sup>âˆ™</sup> AlGaAs resonant tunneling diodes. <i>Applied Physics Letters</i> , 2008, 92, .	1.5	16
213	Effect of annealing on the structural and optical properties of (311)B GaAsBi layers. <i>Applied Surface Science</i> , 2010, 256, 5688-5690.	3.1	16
214	Barrier height and interface characteristics of Au/Mn <sub>5</sub> Ge <sub>3</sub> /Ge (1 1 1) Schottky contacts for spin injection. <i>Semiconductor Science and Technology</i> , 2012, 27, 035014.	1.0	16
215	Effect of nitrogen incorporation on electrical properties of Ti/Au/GaAsN Schottky diodes. <i>Superlattices and Microstructures</i> , 2014, 71, 225-237.	1.4	16
216	Investigation of defects in indium doped TiO <sub>2</sub> thin films using electrical and optical techniques. <i>Journal of Alloys and Compounds</i> , 2017, 698, 883-891.	2.8	16

#	ARTICLE	IF	CITATIONS
217	Hot-electron magnetospectroscopy in resonant tunneling devices: A probe of conduction-band anisotropy. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1989, 7, 1041.	1.6	15
218	Magnetic field and capacitance studies of intrinsic bistability in double-barrier structures. <i>Superlattices and Microstructures</i> , 1989, 6, 59-62.	1.4	15
219	Accurate equivalent circuit model of resonant tunnelling diodes. <i>Electronics Letters</i> , 1991, 27, 427.	0.5	15
220	Far infrared response of double barrier resonant tunneling structures. <i>Surface Science</i> , 1992, 263, 227-230.	0.8	15
221	Microscopic measurement of penetration depth in thin films by scanning Hall probe microscopy. <i>Superconductor Science and Technology</i> , 1997, 10, 17-20.	1.8	15
222	Magneto-photoluminescence and electroluminescence spectroscopy of self-assembled (InGa)As quantum dots on high index planes. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 1998, 2, 662-666.	1.3	15
223	Acoustic phonon-assisted tunneling in GaAs/AlAs superlattices. <i>Physical Review B</i> , 2002, 66, .	1.1	15
224	Magnetic-field-induced miniband conduction in semiconductor superlattices. <i>Physical Review B</i> , 2007, 76, .	1.1	15
225	Electrical properties of nitrogen-related defects in n-type GaAsN grown by molecular-beam epitaxy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009, 6, 2652-2654.	0.8	15
226	Novel multifunctional of magnesium ions (Mg <sup>++</sup> ) incorporated calcium phosphate nanostructures. <i>Journal of Alloys and Compounds</i> , 2018, 730, 31-35.	2.8	15
227	Detailed investigation of defect states in Erbium doped In <sub>2</sub> O <sub>3</sub> thin films. <i>Materials Research Bulletin</i> , 2018, 99, 211-218.	2.7	15
228	From cow manure to bioactive carbon dots: a light-up probe for bioimaging investigations, glucose detection and potential immunotherapy agent for melanoma skin cancer. <i>RSC Advances</i> , 2021, 11, 6346-6352.	1.7	15
229	A microcomputer-based deep level transient spectroscopy (DLTS) system. <i>Journal of Physics E: Scientific Instruments</i> , 1985, 18, 926-929.	0.7	14
230	Investigations of double barrier resonant tunneling devices based on (AlGa)As/GaAs. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1988, 6, 1161.	1.6	14
231	High-magnetic-field studies of hole energy dispersion, cubic anisotropy and space charge build-up in the quantum well of p-type resonant tunnelling devices. <i>Semiconductor Science and Technology</i> , 1992, 7, B413-B417.	1.0	14
232	Resonant magnetotunnelling of electrons and holes in a p-i-n diode device incorporating a double barrier structure. <i>Semiconductor Science and Technology</i> , 1992, 7, B456-B459.	1.0	14
233	All-optical measurement of the giant ambipolar diffusion constant in a hetero-nipi reflection modulator. <i>Semiconductor Science and Technology</i> , 1993, 8, 1750-1754.	1.0	14
234	Landau-level populations and slow energy relaxation of a two-dimensional electron gas probed by tunneling spectroscopy. <i>Physical Review B</i> , 1995, 52, 4666-4669.	1.1	14

#	ARTICLE	IF	CITATIONS
235	Sb-induced GaAs(111)B surface reconstructions: success and failure of the electron-counting rule. Surface Science, 1996, 365, L663-L668.	0.8	14
236	Field penetration and surface barriers in superconducting Bi <sub>2</sub> Sr <sub>2</sub> CaCu <sub>2</sub> O <sub>8</sub> + $\delta$ whiskers. Physical Review B, 1997, 56, R5771-R5773.	1.1	14
237	Substrate orientation dependence of island nucleation critical thickness in strained heterostructures. Europhysics Letters, 1999, 47, 701-707.	0.7	14
238	Experimental studies of the multimode spectral emission in quantum dot lasers. Journal of Applied Physics, 2000, 87, 1943-1946.	1.1	14
239	Photoconductivity of Be-doped GaAs under intense terahertz radiation. Solid State Communications, 2002, 122, 223-228.	0.9	14
240	Light controlled spin polarization in asymmetric n-type resonant tunneling diode. Applied Physics Letters, 2007, 91, .	1.5	14
241	Semiconductor charge transport driven by a picosecond strain pulse. Applied Physics Letters, 2008, 92, 232104.	1.5	14
242	Terahertz acoustic oscillations by stimulated phonon emission in an optically pumped superlattice. Physical Review B, 2009, 79, .	1.1	14
243	Influence of deposition field on the magnetic anisotropy in epitaxial $\text{Co}/\text{GaAs}(001)$ . Physical Review B, 2010, 81, .	1.1	14
244	Investigation of deep-level defects in conductive polymer on n-type 4H- and 6H-silicon carbide substrates using I-V and deep level transient spectroscopy techniques. Journal of Applied Physics, 2012, 112, .	1.1	14
245	Zinc oxide thin films on silicon carbide substrates (ZnO/SiC): electro-optical properties and electrically active defects. Semiconductor Science and Technology, 2014, 29, 045021.	1.0	14
246	Investigation of the effects of gamma radiation on the electrical properties of dilute GaAs $_{1-x}$ N $_x$ layers grown by Molecular Beam Epitaxy. Current Applied Physics, 2015, 15, 1230-1237.	1.1	14
247	Quantised Hall effect and magnetoresistance through a quantum point contact. Journal of Physics Condensed Matter, 1989, 1, 7499-7503.	0.7	13
248	Excited-state spectroscopy of confined shallow donor impurities in a multi-quantum well. Semiconductor Science and Technology, 1990, 5, 305-307.	1.0	13
249	Thermally detected optical absorption and photoluminescence in a GaAs/GaAlAs multi-quantum well sample. Semiconductor Science and Technology, 1993, 8, 1408-1411.	1.0	13
250	Observation of correlated $\nu = 1$ quantum Hall and insulating states in strongly coupled p-type double quantum wells. Surface Science, 1996, 361-362, 117-121.	0.8	13
251	Be doping of (311)A and (100) Al <sub>0.24</sub> Ga <sub>0.76</sub> As grown by molecular beam epitaxy. Applied Physics Letters, 1996, 69, 4215-4217.	1.5	13
252	Manifestations of quantum chaos in resonant tunnelling. Chaos, Solitons and Fractals, 1997, 8, 1381-1411.	2.5	13



#	ARTICLE	IF	CITATIONS
253	Fermi edge singularities in high magnetic fields. <i>Physica B: Condensed Matter</i> , 1998, 256-258, 519-522.	1.3	13
254	Magnetic field quenching of miniband conduction in quasi-one-dimensional superlattices. <i>Physica B: Condensed Matter</i> , 1999, 272, 190-193.	1.3	13
255	Scattering of electrons at a magnetic protuberance of submicron size. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2000, 6, 746-750.	1.3	13
256	Magnetotunneling spectroscopy of an individual quantum dot in a gated tunnel diode. <i>Applied Physics Letters</i> , 2001, 79, 3275-3277.	1.5	13
257	High-field Zeeman contribution to the trion binding energy. <i>Physical Review B</i> , 2002, 65, .	1.1	13
258	Magnetic-Field-Induced Suppression of Electronic Conduction in a Superlattice. <i>Physical Review Letters</i> , 2004, 93, 146801.	2.9	13
259	Magnetophotoluminescence study of the influence of substrate orientation and growth interruption on the electronic properties of InAs $\delta$ -GaAs quantum dots. <i>Journal of Applied Physics</i> , 2004, 96, 2535-2539.	1.1	13
260	Excited states of ring-shaped (InGa)As quantum dots in aGaAs $\delta$ -(AlGa)As quantum well. <i>Physical Review B</i> , 2005, 72, .	1.1	13
261	Growth and characterization of InGaN for photovoltaic devices. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011, 8, 2460-2462.	0.8	13
262	Effect of symmetry reduction on the spin dynamics of (001)-oriented GaAs quantum wells. <i>Physical Review B</i> , 2013, 87, .	1.1	13
263	Enhancement of the luminescence intensity by co-doping Mn <sup>2+</sup> into Er <sup>3+</sup> -doped SrAl <sub>2</sub> O <sub>4</sub> . <i>Journal of Luminescence</i> , 2015, 163, 17-20.	1.5	13
264	Effect of <sup>60</sup> Co $\gamma$ -ray irradiation on electrical properties of Ti/Au/GaAs $\delta$ -xNx Schottky diodes. <i>Current Applied Physics</i> , 2016, 16, 850-858.	1.1	13
265	Resonant magnetotunnelling spectroscopy: a direct probe of the complicated dispersion curves and negative mass behaviour of holes confined in a quantum well. <i>Surface Science</i> , 1992, 263, 199-206.	0.8	12
266	Review article: Wide bandgap electronic materials. <i>Microelectronics Journal</i> , 1992, 23, 500-506.	1.1	12
267	Photoluminescence spectroscopy of self-assembled (InGa)As quantum dots in high magnetic fields. <i>Physica B: Condensed Matter</i> , 1998, 249-251, 262-266.	1.3	12
268	Magnetothermopower of double p-type quantum wells. <i>Physica B: Condensed Matter</i> , 1998, 249-251, 745-748.	1.3	12
269	Longitudinal and Hall resistance induced by large-amplitude magnetic barriers. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2000, 6, 755-758.	1.3	12
270	Dependence of quantum-dot formation on substrate orientation studied by magnetophotoluminescence. <i>Applied Physics Letters</i> , 2002, 81, 1480-1482.	1.5	12



#	ARTICLE	IF	CITATIONS
271	Tunneling spectroscopy of mixed stable-chaotic electron dynamics in a quantum well. Physical Review B, 2002, 65, .	1.1	12
272	Magneto spectroscopy of Be in GaAs. Physical Review B, 2003, 67, .	1.1	12
273	Current flow and energy dissipation in low-dimensional semiconductor superlattices. Applied Physics Letters, 2006, 88, 052111.	1.5	12
274	Deep-level Transient Spectroscopy of GaAs/AlGaAs Multi-Quantum Wells Grown on (100) and (311)B GaAs Substrates. Nanoscale Research Letters, 2010, 5, 1948-1951.	3.1	12
275	Dispersive line shape in the vicinity of the $\nu = 1/2$ Hall state: Coexistence of Knight-shifted and unshifted resistively detected NMR responses. Physical Review B, 2013, 88, .	1.1	12
276	Deep-level transient spectroscopy of interfacial states in $\delta$ -buffer-free p-i-n GaSb/GaAs devices. Journal of Applied Physics, 2013, 114, 134507.	1.1	12
277	Identification of nitrogen- and host-related deep-level traps in n-type GaNAs and their evolution upon annealing. Journal of Applied Physics, 2014, 116, 013705.	1.1	12
278	Far-infrared photoconductivity spectroscopy of high-mobility n-GaAs grown by MBE. Semiconductor Science and Technology, 1989, 4, 548-552.	1.0	11
279	High magnetic field studies of resonant tunneling via shallow impurities in $\delta$ -doped quantum wells. Physica B: Condensed Matter, 1993, 184, 241-245.	1.3	11
280	Mesoscopic effects in resonant tunnelling diodes. Solid-State Electronics, 1994, 37, 965-968.	0.8	11
281	A comparison of Si-doped (100), (111) A, (111) B and (311) B Al <sub>x</sub> Ga <sub>1-x</sub> As samples grown by molecular beam epitaxy. Semiconductor Science and Technology, 1995, 10, 49-55.	1.0	11
282	Magnetotunnelling and Photoluminescence Spectroscopy of Self-Assembled InAs Quantum Dots. Japanese Journal of Applied Physics, 1997, 36, 4073-4077.	0.8	11
283	Observation of giant oscillations in the phonon-induced conductivity of a GaAs quantum wire. Physical Review B, 1997, 55, 9775-9778.	1.1	11
284	Intrinsic Polarised Emission from InAs/GaAs(311)A Quantum Dots. Japanese Journal of Applied Physics, 1999, 38, 4676-4679.	0.8	11
285	Transverse threshold for sliding conduction in a magnetically induced Wigner solid. Physica B: Condensed Matter, 2000, 284-288, 1984-1985.	1.3	11
286	3D island nucleation behaviour on high index substrates. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2000, 74, 239-241.	1.7	11
287	Exploiting low dimensional structures and devices. III-Vs Review, 2000, 13, 40-44.	0.1	11
288	Magnetic-field-induced recovery of resonant tunneling into a disordered quantum well subband. Physical Review B, 2003, 68, .	1.1	11

#	ARTICLE	IF	CITATIONS
289	Effect of inter-miniband tunneling on current resonances due to the formation of stochastic conduction networks in superlattices. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2006, 32, 285-288.	1.3	11
290	Influence of the single-particle Zeeman energy on the quantum Hall ferromagnet at high filling factors. <i>Physical Review B</i> , 2007, 75, .	1.1	11
291	Nonlinear birefringence and time-resolved Kerr measurement of spin lifetimes in (110)GaAs/AlyGa1- $\alpha$ As quantum wells. <i>Physical Review B</i> , 2010, 81, .	1.1	11
292	Picosecond strain pulses probed by the photocurrent in semiconductor devices with quantum wells. <i>Physical Review B</i> , 2011, 83, .	1.1	11
293	Spin injection from two-dimensional electron and hole gases in resonant tunneling diodes. <i>Applied Physics Letters</i> , 2011, 99, 233507.	1.5	11
294	Deep levels in H-irradiated GaAs <sub>1-x</sub> N <sub>x</sub> ( $x \leq 0.01$ ) grown by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2011, 110, .	1.1	11
295	Quantum oscillations in the photocurrent of GaAs/AlAs p-n diodes. <i>Physical Review B</i> , 2014, 89, .	1.1	11
296	Influence of annealing temperature on electrical characteristics of Ti/Au/GaAsN Schottky diode with 0.2% nitrogen incorporation. <i>Materials Science in Semiconductor Processing</i> , 2014, 22, 92-100.	1.9	11
297	High-performance organic/inorganic hybrid heterojunction based on Gallium Arsenide (GaAs) substrates and a conjugated polymer. <i>Applied Surface Science</i> , 2015, 357, 2189-2197.	3.1	11
298	Investigation of electrically active defects in InGaAs quantum wire intermediate-band solar cells using deep-level transient spectroscopy technique. <i>Nanotechnology</i> , 2017, 28, 045707.	1.3	11
299	The observation of the fractional quantum Hall effect in a single (AlGa)As/GaAs/(AlGa)As quantum well. <i>Semiconductor Science and Technology</i> , 1990, 5, 792-794.	1.0	10
300	Optical investigation of a very asymmetric double-barrier resonant-tunneling structure. <i>Physical Review B</i> , 1992, 45, 6721-6730.	1.1	10
301	Quantum well luminescence at acceptors in p-i-n resonant tunnelling diodes. <i>Semiconductor Science and Technology</i> , 1994, 9, 555-558.	1.0	10
302	High magnetic field millimetre and submillimetre spectroscopy of ultra-high mobility 2D hole systems. <i>Physica B: Condensed Matter</i> , 1995, 211, 440-443.	1.3	10
303	Millikelvin magneto-optical studies of two-dimensional hole systems. <i>Physical Review B</i> , 1996, 54, 13891-13898.	1.1	10
304	Photoluminescence investigation of Si as p-type dopant in AlGaAs grown by molecular beam epitaxy on high-index planes. <i>Semiconductor Science and Technology</i> , 1996, 11, 1830-1837.	1.0	10
305	Studies of Phonon-Assisted Tunnelling in a $\delta$ -Doped Double Barrier Resonant Tunnelling Device. <i>Physica Status Solidi (B): Basic Research</i> , 1997, 204, 431-434.	0.7	10
306	Giant magnetoresistance and hysteretic effects in hybrid semiconductor/ferromagnet devices. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 1998, 2, 421-425.	1.3	10

#	ARTICLE	IF	CITATIONS
307	Microwave absorption in the magnetically-induced Wigner solid phase of a two-dimensional hole system. <i>Physica B: Condensed Matter</i> , 1998, 249-251, 53-56.	1.3	10
308	Quantum Hall effect breakdown in two-dimensional hole gases. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2000, 6, 136-139.	1.3	10
309	Quantum dot nanostructures. <i>Materials Today</i> , 2002, 5, 48-53.	8.3	10
310	Use of stochastic web patterns to control electron transport in semiconductor superlattices. <i>Physica D: Nonlinear Phenomena</i> , 2004, 199, 166-172.	1.3	10
311	Magneto-photoluminescence of stacked self-assembled InAs/GaAs quantum dots. <i>Physica B: Condensed Matter</i> , 2004, 346-347, 428-431.	1.3	10
312	Spin splitting of X-valley-related donor impurity states in an AlAs barrier. <i>Physical Review B</i> , 2005, 71, .	1.1	10
313	Angle dependence of acoustic phonon-assisted tunneling in a weakly coupled superlattice: Evidence for terahertz phonon amplification. <i>Journal of Applied Physics</i> , 2005, 98, 033514.	1.1	10
314	Temperature dependence of the photoluminescence of self-assembled InAs/GaAs quantum dots in pulsed magnetic fields. <i>Physical Review B</i> , 2008, 77, .	1.1	10
315	Magneto-optical properties of GaBiAs layers. <i>Journal Physics D: Applied Physics</i> , 2014, 47, 075103.	1.3	10
316	Effect of gamma radiation on the electrical properties of Polyaniline/silicon carbide heterojunctions. <i>Radiation Measurements</i> , 2014, 71, 402-406.	0.7	10
317	Analysis of Deep Level Defects in GaN p-i-n Diodes after Beta Particle Irradiation. <i>Electronics (Switzerland)</i> , 2015, 4, 1090-1100.	1.8	10
318	Phonon emission by a hot two dimensional electron gas at the gallium arsenide/aluminium gallium arsenide interface. <i>Solid-State Electronics</i> , 1989, 32, 1755-1759.	0.8	9
319	Resonant subband Landau level coupling in GaAs-(Ga,Al)As quantum wells in tilted magnetic fields. <i>Semiconductor Science and Technology</i> , 1991, 6, 208-217.	1.0	9
320	Asymmetry in the I(V) characteristics of a gated resonant tunnelling diode. <i>Semiconductor Science and Technology</i> , 1992, 7, B442-B445.	1.0	9
321	Contact resistance to high-mobility AlGaAs/GaAs heterostructures. <i>Semiconductor Science and Technology</i> , 1992, 7, 1085-1090.	1.0	9
322	Transport in sub-micron resonant tunnelling devices. <i>Physica B: Condensed Matter</i> , 1993, 189, 125-134.	1.3	9
323	Photoluminescence of donor energy levels in resonant tunnelling devices. <i>Semiconductor Science and Technology</i> , 1994, 9, 549-551.	1.0	9
324	Magnetic-field dependence of the electrical characteristics of a gated resonant-tunneling diode. <i>Physical Review B</i> , 1994, 49, 2261-2264.	1.1	9

#	ARTICLE	IF	CITATIONS
325	Intrinsic bistability in the electroluminescence spectrum and current-voltage characteristics of triple-barrier p-i-n resonant tunneling devices. <i>Surface Science</i> , 1994, 305, 353-357.	0.8	9
326	The growth and physics of ultra-high-mobility two-dimensional hole gas on (311) A GaAs surface. <i>Journal of Crystal Growth</i> , 1995, 150, 451-454.	0.7	9
327	Dynamics of individual vortices and flux bundles in Nb films. <i>Superconductor Science and Technology</i> , 1995, 8, 459-463.	1.8	9
328	Vortex imaging in superconducting films by scanning hall probe microscopy. <i>Journal of Low Temperature Physics</i> , 1996, 105, 1135-1140.	0.6	9
329	Island, trimer, and chain formation on the Sb-terminated GaAs(111)B surface. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1996, 14, 1024.	1.6	9
330	Heat-pulse study of the phonon emission by hot two-dimensional holes in a gallium arsenide heterojunction. <i>Semiconductor Science and Technology</i> , 1997, 12, 849-857.	1.0	9
331	Photoluminescence investigation of Si-doped GaAs grown by molecular beam epitaxy on non-(100) oriented surfaces. <i>Microelectronics Journal</i> , 1997, 28, 717-726.	1.1	9
332	Spectroscopic studies of self-assembled InAs and In <sub>0.5</sub> Ga <sub>0.5</sub> As quantum dots. <i>Applied Surface Science</i> , 1998, 123-124, 366-370.	3.1	9
333	Stimulated phonon emission in superlattices. <i>Physica B: Condensed Matter</i> , 1999, 263-264, 537-539.	1.3	9
334	Phonon emission by warm electrons in GaAs quantum wells: the effect of well width on the acoustic-optic crossover. <i>Physica B: Condensed Matter</i> , 1999, 263-264, 526-529.	1.3	9
335	Energy levels of negatively charged excitons in high magnetic fields. <i>Solid State Communications</i> , 2000, 115, 403-406.	0.9	9
336	Conductance fluctuations in a double-barrier resonant tunneling device. <i>Physical Review B</i> , 2000, 62, 16721-16726.	1.1	9
337	Electrical transport of 2D electrons in non-uniform magnetic fields. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2001, 11, 171-176.	1.3	9
338	Acoustic Phonon Emission by Optically Excited Carriers in the InAs/GaAs Quantum Dot System. <i>Physica Status Solidi (B): Basic Research</i> , 2001, 224, 659-663.	0.7	9
339	Microwave and transport studies of the magnetically-induced insulating phase of bilayer hole systems. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2002, 12, 296-299.	1.3	9
340	Built-in electric fields in InAs quantum dots grown on (N11) GaAs substrates. <i>Microelectronics Journal</i> , 2002, 33, 583-588.	1.1	9
341	Monochromatic transverse-polarized phonons from femtosecond pulsed optical excitation of a GaAs/AlAs superlattice. <i>Physical Review B</i> , 2004, 69, .	1.1	9
342	Gated spin relaxation in (110)-oriented quantum wells. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2004, 23, 309-314.	1.3	9

#	ARTICLE	IF	CITATIONS
343	Energy-dependent electron-electron scattering and spin dynamics in a two-dimensional electron gas. <i>Physical Review B</i> , 2008, 77, .	1.1	9
344	Structural and magnetic properties of magnetron sputtered Co <sub>70</sub> Fe <sub>30</sub> films on GaAs(110). <i>Journal of Applied Physics</i> , 2009, 105, 073907.	1.1	9
345	Photomodulated transmittance of GaBiAs layers grown on (001) and (311)B GaAs substrates. <i>Microelectronics Journal</i> , 2009, 40, 537-539.	1.1	9
346	Electrical characterisation of deep level defects in Be-doped AlGaAs grown on (100) and (311)A GaAs substrates by MBE. <i>Nanoscale Research Letters</i> , 2011, 6, 180.	3.1	9
347	Deep traps and temperature effects on the capacitance of p-type Si-doped GaAs Schottky diodes on (211) and (311) oriented GaAs substrates. <i>Superlattices and Microstructures</i> , 2014, 65, 319-331.	1.4	9
348	Modeling the effect of deep traps on the capacitance-voltage characteristics of p-type Si-doped GaAs Schottky diodes grown on high index GaAs substrates. <i>Materials Science in Semiconductor Processing</i> , 2015, 36, 156-161.	1.9	9
349	Negative activation energy and dielectric signatures of excitons and excitonic Mott transitions in quantum confined laser structures. <i>Journal of Applied Physics</i> , 2016, 120, 144304.	1.1	9
350	Investigation of the structural, optical and electrical properties of indium-doped TiO <sub>2</sub> thin films grown by Pulsed Laser Deposition technique on low and high index GaAs planes. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2020, 259, 114578.	1.7	9
351	Analysis of I-V characteristics of Be-doped AlGaAs Schottky diodes grown on (100) GaAs substrates by molecular beam epitaxy. <i>Microelectronics Journal</i> , 2022, 122, 105409.	1.1	9
352	Quantum interference and space charge effects in double barrier structures incorporating wide quantum wells. <i>Solid-State Electronics</i> , 1989, 32, 1627-1631.	0.8	8
353	Double-barrier resonant tunnelling diode three-state logic. <i>Electronics Letters</i> , 1990, 26, 61-62.	0.5	8
354	Hot hole effects in single barrier p-type GaAs/(AlGa)As/GaAs tunnel structures. <i>Applied Physics Letters</i> , 1991, 59, 3124-3126.	1.5	8
355	Nonlinear conductance of quantum point contacts in a magnetic field. <i>Semiconductor Science and Technology</i> , 1992, 7, B279-B282.	1.0	8
356	A direct comparison of the quantized Hall resistance in high critical current gallium arsenide and silicon devices. <i>Surface Science</i> , 1992, 263, 112-115.	0.8	8
357	Tunneling spectroscopy of energy levels in wide quantum wells in tilted magnetic fields. <i>Physical Review B</i> , 1992, 45, 8749-8751.	1.1	8
358	Title is missing!. <i>Journal of Physics Condensed Matter</i> , 1993, 5, L449-L456.	0.7	8
359	Far-infrared emission from two-dimensional electron and hole gases in GaAs/(AlGa)As heterojunctions. <i>Semiconductor Science and Technology</i> , 1994, 9, 831-834.	1.0	8
360	Photohole-induced resonant tunneling of electrons in selectively etched small area GaAs/AlAs double barrier diodes. <i>Solid-State Electronics</i> , 1994, 37, 973-976.	0.8	8

#	ARTICLE	IF	CITATIONS
361	Molecular beam epitaxy growth and properties of GaAs/(AlGa)As p-type heterostructures on (100), (011), (111)B, (211)B, (311)B, and (311)A oriented GaAs. <i>Journal of Crystal Growth</i> , 1995, 150, 446-450.	0.7	8
362	Phonoconductivity measurements of the electron-phonon interaction in quantum wire structures. <i>Surface Science</i> , 1996, 361-362, 660-663.	0.8	8
363	Farâ€infrared intersubband transitions in a twoâ€dimensional GaAs/(Al,Ga)As hole system: Direct comparison of experiment and calculation. <i>Journal of Applied Physics</i> , 1996, 80, 6058-6060.	1.1	8
364	Resonant magnetotunneling through individual self-assembled InAs quantum dots. <i>Superlattices and Microstructures</i> , 1997, 21, 255-258.	1.4	8
365	Size-effects and tuning of phase coherence in a double quantum well mesoscopic wire. <i>Physica B: Condensed Matter</i> , 1998, 249-251, 162-165.	1.3	8
366	Many-body effects in a quantised 2DES probed by discrete-level tunnelling spectroscopy. <i>Physica B: Condensed Matter</i> , 1998, 249-251, 689-692.	1.3	8
367	Phase coherence in double quantum well mesoscopic wires. <i>Physica B: Condensed Matter</i> , 1998, 256-258, 413-416.	1.3	8
368	Optical and morphological properties of In(Ga)As/GaAs quantum dots grown on novel index surfaces. <i>Microelectronics Journal</i> , 1999, 30, 419-425.	1.1	8
369	Transport properties of a two-dimensional electron gas due to a spatially random magnetic field. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2000, 6, 751-754.	1.3	8
370	Universality of the Stokes Shift for a Disordered Ensemble of Quantum Dots. <i>Physica Status Solidi (B): Basic Research</i> , 2001, 224, 41-45.	0.7	8
371	Double injection currents in p-i-n diodes incorporating self-assembled quantum dots. <i>Nanotechnology</i> , 2001, 12, 515-517.	1.3	8
372	Measurements of composite fermion masses from the spin polarization of two-dimensional electrons in the region $1 < \nu < 2$ . <i>Physical Review B</i> , 2002, 65, .	1.1	8
373	Emission energy and polarization tuning of InAs/GaAs self-assembled quantum dots by growth interruption. <i>Journal of Crystal Growth</i> , 2003, 251, 192-195.	0.7	8
374	Novel breakdown of the quantum Hall effect: An example of self-organised criticality?. <i>Europhysics Letters</i> , 2006, 75, 287-293.	0.7	8
375	Sharp-line electroluminescence from individual quantum dots by resonant tunneling injection of carriers. <i>Applied Physics Letters</i> , 2006, 89, 092106.	1.5	8
376	Electrical performance of conducting polymer (SPAN) grown on GaAs with different substrate orientations. <i>Applied Surface Science</i> , 2016, 387, 228-236.	3.1	8
377	Impact of doping on the performance of p-type Be-doped Al 0.29 Ga 0.71 As Schottky diodes. <i>Modern Electronic Materials</i> , 2017, 3, 66-71.	0.2	8
378	Magnetic Field Studies of Resonant and Non-resonant Tunnelling in n-(AlGa)As/GaAs Double Barrier Structures. <i>Springer Series in Solid-state Sciences</i> , 1988, , 74-83.	0.3	8

#	ARTICLE	IF	CITATIONS
379	Resonant and non-resonant processes in double barrier structures. Superlattices and Microstructures, 1989, 6, 63-66.	1.4	7
380	Impedance analysis of GaAs/Al(Ga)As resonant tunnel diodes in the NDR region. Electronics Letters, 1990, 26, 1522.	0.5	7
381	Influence of scattering on the I-V characteristics of double-barrier resonant-tunneling diodes. Physica B: Condensed Matter, 1991, 175, 301-306.	1.3	7
382	Photon-assisted tunnelling in sequential resonant tunnelling devices. Semiconductor Science and Technology, 1992, 7, 432-435.	1.0	7
383	Substrate temperature dependence of the minority carrier lifetime in (AlGa)As/GaAs MQWs grown with As <sub>2</sub> and As <sub>4</sub> . Journal of Crystal Growth, 1993, 127, 841-844.	0.7	7
384	Intrinsic bistability and hole-charge buildup in asymmetric p-type resonant-tunneling structures. Physical Review B, 1994, 49, 10745-10748.	1.1	7
385	External photoluminescence efficiency and minority carrier lifetime of (Al,Ga)As/GaAs multi-quantum-well samples grown by molecular beam epitaxy using both As <sub>2</sub> and As <sub>4</sub> . Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1994, 12, 1026.	1.6	7
386	High efficiency submicron light-emitting resonant tunneling diodes. Applied Physics Letters, 1994, 65, 3332-3334.	1.5	7
387	Enhancement of spin-dependent hole delocalization in degenerate asymmetric double quantum wells. Physical Review B, 1996, 53, 10000-10007.	1.1	7
388	Observation of resonant hole tunnelling through a (110) oriented AlAs/GaAs/AlAs quantum well. Semiconductor Science and Technology, 1996, 11, 1424-1428.	1.0	7
389	Magneto-Spectroscopy of Beryllium Impurity in Gallium Arsenide. Physica Status Solidi (B): Basic Research, 1998, 210, 821-825.	0.7	7
390	Saturation absorption studies of intersubband relaxation rates in a p-GaAs/AlGaAs QW using a free electron laser. Physica E: Low-Dimensional Systems and Nanostructures, 1998, 2, 181-185.	1.3	7
391	Interband spectroscopy of p-type GaAs/(Al,Ga)As quantum wells at low hole densities. Physica B: Condensed Matter, 1998, 249-251, 607-611.	1.3	7
392	Tunneling current bistability of correlated 2D electron-hole layers. Physica B: Condensed Matter, 1998, 256-258, 531-534.	1.3	7
393	Enhancement of luminescence intensity induced by 1.06 $\mu\text{m}$ excitation in InAs/GaAs quantum dots. Semiconductor Science and Technology, 1999, 14, 1132-1135.	1.0	7
394	Measurement of the Hall current density in a Corbino geometry 2D electron gas. Physical Review B, 1999, 59, 7323-7326.	1.1	7
395	Pressure-Induced $\gamma$ -X Crossover in Self-Assembled In(Ga)As/GaAs Quantum Dots. Physica Status Solidi (B): Basic Research, 1999, 211, 79-83.	0.7	7
396	Magnetic field variation of tunnelling gap between disordered two-dimensional electron systems. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 6, 602-605.	1.3	7



#	ARTICLE	IF	CITATIONS
397	Tunneling spectroscopy of quasi-two-dimensional plasmons. <i>Physics-Uspexhi</i> , 2001, 44, 1301-1304.	0.8	7
398	Giant magnetoresistance induced by magnetic barriers. <i>IEEE Transactions on Magnetism</i> , 2001, 37, 1992-1994.	1.2	7
399	Resonant tunneling diode circuits using Pspice. <i>Microelectronics Journal</i> , 2003, 34, 741-745.	1.1	7
400	Anisotropic magnetoresistance in a two-dimensional electron gas in a quasirandom magnetic field. <i>Physical Review B</i> , 2004, 70, .	1.1	7
401	Depolarization of the ground state in the quantum Hall ferromagnet and its dependence on g-factor. <i>Semiconductor Science and Technology</i> , 2004, 19, 252-255.	1.0	7
402	noise in a dilute GaAs two-dimensional hole system in the insulating phase. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2006, 34, 252-255.	1.3	7
403	Optical detection of folded mini-zone-edge coherent acoustic modes in a doped GaAs/AlAs superlattice. <i>Physical Review B</i> , 2010, 82, .	1.1	7
404	Absorption and photoluminescence spectroscopy of Er <sup>3+</sup> -doped SrAl <sub>2</sub> O <sub>4</sub> ceramic phosphors. <i>Philosophical Magazine Letters</i> , 2012, 92, 194-201.	0.5	7
405	Comparative optical studies of InGaAs/GaAs quantum wells grown by MBE on (100) and (311)A GaAs planes. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012, 9, 1621-1623.	0.8	7
406	Strain and localization effects in InGaAs(N) quantum wells: Tuning the magnetic response. <i>Journal of Applied Physics</i> , 2014, 116, .	1.1	7
407	Dynamics of electronic transitions and frequency dependence of negative capacitance in semiconductor diodes under high forward bias. <i>Applied Physics Letters</i> , 2014, 105, .	1.5	7
408	Optical properties of GaAs <sub>1-x</sub> Bi <sub>x</sub> /GaAs quantum well structures grown by molecular beam epitaxy on (100) and (311)B GaAs substrates. <i>Semiconductor Science and Technology</i> , 2018, 33, 124015.	1.0	7
409	The effect of As on Zn diffusion-induced disordering of AlAs/GaAs superlattices. <i>Semiconductor Science and Technology</i> , 1990, 5, 561-565.	1.0	6
410	Subnanosecond far infrared photoconductivity from a GaAs/AlGaAs multiquantum well. <i>Journal of Applied Physics</i> , 1990, 68, 1913-1915.	1.1	6
411	High pressure studies of resonant tunnelling and superlattice phenomena. <i>Semiconductor Science and Technology</i> , 1991, 6, 422-427.	1.0	6
412	Electron transport in double-barrier resonant tunnelling structures studied by optical spectroscopy. <i>Semiconductor Science and Technology</i> , 1992, 7, B401-B408.	1.0	6
413	Electroluminescence and magnetotransport studies of a p-i-n superlattice double-barrier resonant tunnelling structure. <i>Semiconductor Science and Technology</i> , 1994, 9, 540-544.	1.0	6
414	Heat pulse studies of the energy relaxation of hot 2D holes in a GaAs/(AlGa)As heterojunction by phonon emission. <i>Semiconductor Science and Technology</i> , 1994, 9, 786-788.	1.0	6



#	ARTICLE	IF	CITATIONS
415	Studies of the asymmetry of phonon emission from hot carriers in the quantum Hall regime of GaAs. <i>Semiconductor Science and Technology</i> , 1994, 9, 800-802.	1.0	6
416	Luminescence studies of resonant tunneling in a triple barrier structure with strongly coupled quantum wells. <i>Solid-State Electronics</i> , 1994, 37, 721-724.	0.8	6
417	Effective-mass anisotropy in GaAs-(Ga,Al)As two-dimensional hole systems: comparison of theory and very high-field cyclotron resonance experiments. <i>Journal of Physics Condensed Matter</i> , 1995, 7, L675-L681.	0.7	6
418	Photoluminescence determination of the Be binding energy in direct-gap AlGaAs. <i>Applied Physics Letters</i> , 1997, 71, 3120-3122.	1.5	6
419	Many-body blockade of resonant tunneling of two-dimensional electrons. <i>Physical Review B</i> , 1997, 56, 1053-1056.	1.1	6
420	Phonon Emission by Hot Two-Dimensional Electrons in Gallium-Arsenide Devices: The Mystery of the Missing Longitudinal Mode. <i>Physica Status Solidi (B): Basic Research</i> , 1997, 204, 230-233.	0.7	6
421	Magneto-Optical Study of Correlated Electron-Hole Layers in Single-Barrier Heterostructures. <i>Physica Status Solidi A</i> , 1997, 164, 587-590.	1.7	6
422	Capacitance-voltage studies of the electrostatic profile of single barrier GaAs/AlAs/GaAs structures containing self assembled quantum dots. <i>Solid-State Electronics</i> , 1998, 42, 1293-1295.	0.8	6
423	High field magnetoluminescence spectroscopy of self-assembled (InGa)As quantum dots on high index planes. <i>Physica B: Condensed Matter</i> , 1998, 246-247, 93-96.	1.3	6
424	Skyrmion excitations in the limit of vanishing Landé g-factor. <i>Physica B: Condensed Matter</i> , 1998, 249-251, 1-6.	1.3	6
425	Voltage-controlled sharp-line electroluminescence in GaAs-AlAs double-barrier resonant-tunneling structures. <i>Physical Review B</i> , 1998, 58, R4242-R4245.	1.1	6
426	Wavelength tuning in GaAs/AlGaAs quantum wells by InAs submonolayer insertion. <i>Journal of Physics Condensed Matter</i> , 1999, 11, 3629-3633.	0.7	6
427	Measuring the size of buried quantum dots using phonons. <i>Physica B: Condensed Matter</i> , 1999, 263-264, 514-516.	1.3	6
428	Electron and hole levels of InAs quantum dots in a GaAs matrix. <i>Superlattices and Microstructures</i> , 1999, 25, 105-111.	1.4	6
429	The transport of 2D electrons through magnetic barriers. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2000, 7, 997-1000.	1.3	6
430	Low-frequency impedance of quantized Hall conductors. <i>Physical Review B</i> , 2000, 62, 12990-12996.	1.1	6
431	Positively charged defects associated with self-assembled quantum dot formation. <i>Applied Physics Letters</i> , 2000, 76, 3570-3572.	1.5	6
432	Photoresponse spectra in p-i-n diodes containing quantum dots. <i>Nanotechnology</i> , 2002, 13, 94-96.	1.3	6

#	ARTICLE	IF	CITATIONS
433	Quantum Hall effect breakdown: can the bootstrap heating and inter-Landau-level scattering models be reconciled?. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2002, 12, 178-181.	1.3	6
434	Measuring the energy levels and wave functions in a single quantum dot. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2002, 13, 634-637.	1.3	6
435	Self-assembled quantum dots on GaAs for optoelectronic applications. <i>Microelectronics Journal</i> , 2003, 34, 333-336.	1.1	6
436	BREAKDOWN OF THE QUANTUM HALL EFFECTS IN HOLE SYSTEMS AT HIGH INDUCED CURRENTS. <i>International Journal of Modern Physics B</i> , 2004, 18, 3537-3540.	1.0	6
437	Resonance-like piezoelectric electron-phonon interaction in layered structures. <i>Physical Review B</i> , 2006, 74, .	1.1	6
438	In-plane magnetic anisotropies of sputtered Co <sub>0.7</sub> Fe <sub>0.3</sub> films on AlGaAs(001) spin light emitting diode heterostructures. <i>Journal of Applied Physics</i> , 2007, 101, 09D106.	1.1	6
439	Dilute (In,Ga)(As,N) thin films grown by molecular beam epitaxy on (100) and non-(100) GaAs substrates: a Raman-scattering study. <i>Journal of Materials Science: Materials in Electronics</i> , 2009, 20, 116-119.	1.1	6
440	Optical Imaging of Electrical Carrier Injection into Individual InAs Quantum Dots. <i>Physical Review Letters</i> , 2010, 105, 257401.	2.9	6
441	Micro-photoluminescence of GaInNAs layers grown on GaAs substrates of various crystallographic orientations. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011, 8, 1655-1658.	0.8	6
442	Anomalous optical properties of GaMnAs/AlAs quantum wells grown by molecular beam epitaxy. <i>Journal Physics D: Applied Physics</i> , 2012, 45, 215301.	1.3	6
443	Photoluminescence intensity enhancement in self-assembled InAs quantum dots grown on (311)B and (100) GaAs substrates and coated with gold nanoparticles. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2013, 54, 233-236.	1.3	6
444	Classical percolation fingerprints in the high temperature regime of the quantum Hall effect. <i>New Journal of Physics</i> , 2013, 15, 083027.	1.2	6
445	Mechanism of periodic height variations along self-aligned VLS-grown planar nanostructures. <i>Nanoscale</i> , 2015, 7, 20442-20450.	2.8	6
446	Polarization resolved photoluminescence in GaAs <sub>1-x</sub> Bi <sub>x</sub> /GaAs quantum wells. <i>Journal of Luminescence</i> , 2017, 182, 49-52.	1.5	6
447	Effect of thermal annealing on the optical and structural properties of (311)B and (001) GaAsBi/GaAs single quantum wells grown by MBE. <i>Journal of Applied Physics</i> , 2020, 127, 125704.	1.1	6
448	A transient thermal failure mode in metal film resistors. <i>Journal Physics D: Applied Physics</i> , 1987, 20, 1454-1456.	1.3	5
449	The observation of electroluminescence in a double barrier resonant tunnelling structure. <i>Superlattices and Microstructures</i> , 1990, 8, 391-394.	1.4	5
450	The effect of conduction band anisotropy on hybrid magneto-electric states in resonant tunneling devices. <i>Surface Science</i> , 1990, 228, 433-436.	0.8	5

#	ARTICLE	IF	CITATIONS
451	Zero dimensional resonant tunneling through single donor states. Superlattices and Microstructures, 1992, 11, 149-153.	1.4	5
452	Observation of the fractional quantum Hall effect in GaAs-(Ga, Al)As quantum well structures. Physica B: Condensed Matter, 1993, 184, 81-85.	1.3	5
453	Observation of a spin polarization phase transition of the 4/3 fractional quantum Hall state in a high-mobility 2D hole system. Journal of Physics Condensed Matter, 1993, 5, L565-L570.	0.7	5
454	Quantum well luminescence due to minority photoelectrons in p-type resonant tunnelling structures. Semiconductor Science and Technology, 1994, 9, 552-554.	1.0	5
455	Quantum transport of p-type GaAs/(AlGa)As heterostructures grown on non-(100) substrates by molecular beam epitaxy. Microelectronics Journal, 1995, 26, 739-744.	1.1	5
456	Evidence for composite fermions from the magnetothermopower of 2D holes. Surface Science, 1996, 361-362, 50-54.	0.8	5
457	Non-equilibrium acoustic phonon-assisted tunnelling in GaAs/(AlGa)As double barrier devices. Surface Science, 1996, 361-362, 181-184.	0.8	5
458	Magneto-tunnelling spectroscopy of a quantum dot charged with a few electrons. Surface Science, 1996, 361-362, 644-647.	0.8	5
459	Mesoscopic conductance fluctuations in impurity-assisted resonant tunnelling. Solid-State Electronics, 1996, 40, 409-412.	0.8	5
460	Operation and theoretical analysis of the multiple asymmetric coupled quantum-well light modulator in the n-i-n configuration. IEEE Journal of Quantum Electronics, 1997, 33, 1084-1088.	1.0	5
461	Molecular beam epitaxy: from research to manufacturing. Thin Solid Films, 1997, 306, 331-337.	0.8	5
462	Self-aggregation of InAs quantum dots on (N11) GaAs substrates. Thin Solid Films, 1998, 336, 9-12.	0.8	5
463	Magneto-acoustic phonon antiresonances in Wannier's Stark superlattices. Solid-State Electronics, 1998, 42, 1489-1493.	0.8	5
464	Magneto-tunnelling spectroscopy of single self-assembled InAs quantum dots in AlAs. Physica E: Low-Dimensional Systems and Nanostructures, 1998, 2, 657-661.	1.3	5
465	Composite fermion signature in the acoustoelectric effect in 2DES and 2DHS. Physica B: Condensed Matter, 1998, 249-251, 36-39.	1.3	5
466	Hall effect of pinned and depinned 2-D electron and hole solids. Physica B: Condensed Matter, 1998, 256-258, 587-590.	1.3	5
467	Magneto-tunnelling spectroscopy of a two-dimensional electron system. Physica B: Condensed Matter, 1998, 256-258, 507-513.	1.3	5
468	Influence of surface barriers on vortex dynamics in Bi/sub 2/Sr/sub 2/CaCu/sub 2/O/sub 8+Î´ whiskers. IEEE Transactions on Applied Superconductivity, 1999, 9, 2671-2673.	1.1	5

#	ARTICLE	IF	CITATIONS
469	Zeeman spectroscopy of the Be acceptor in GaAs to intermediate fields. <i>Solid State Communications</i> , 1999, 112, 25-29.	0.9	5
470	Effect of the substrate orientation on the self-organisation of (InGa)As/GaAs quantum dots. <i>Microelectronics Journal</i> , 1999, 30, 319-322.	1.1	5
471	Luminescence tuning of InAs/GaAs quantum dots grown on high-index planes. <i>Superlattices and Microstructures</i> , 1999, 25, 113-117.	1.4	5
472	Suppression of electron injection into a finite superlattice in an applied magnetic field. <i>Physical Review B</i> , 2001, 63, .	1.1	5
473	Scanning capacitance imaging of compressible quantum Hall effect stripes formed at the sample edge and at a potential fluctuation. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2008, 40, 1548-1550.	1.3	5
474	Role of $X$ valley on the dynamics of electron transport through a GaAs/AlAs double-barrier structure. <i>Physical Review B</i> , 2008, 78, .	1.1	5
475	Time-domain THz spectroscopy using acceptor-doped GaAs photoconductive emitters. <i>Semiconductor Science and Technology</i> , 2008, 23, 105012.	1.0	5
476	Fermi-edge singularity at tunneling and anisotropic magneto-tunneling in low-dimensional semiconductor structures. <i>Physica Scripta</i> , 2010, 82, 038106.	1.2	5
477	Enhancement of activation energies of sharp photoluminescence lines for GaInNAs quantum wells due to quantum confinement. <i>Journal Physics D: Applied Physics</i> , 2013, 46, 402001.	1.3	5
478	Period of photoconductivity oscillations and charge dynamics of quantum dots in GaAs/InAs/AlAs heterojunctions. <i>JETP Letters</i> , 2015, 102, 720-726.	0.4	5
479	Rapid thermal annealing: An efficient method to improve the electrical properties of tellurium compensated Interfacial Misfit GaSb/GaAs heterostructures. <i>Superlattices and Microstructures</i> , 2015, 88, 80-89.	1.4	5
480	Spin polarization of carriers in resonant tunneling devices containing InAs self-assembled quantum dots. <i>Superlattices and Microstructures</i> , 2015, 88, 574-581.	1.4	5
481	W line shape in the resistively detected nuclear magnetic resonance. <i>Journal of Physics Condensed Matter</i> , 2015, 27, 275801.	0.7	5
482	Electrical Behavior of MBE Grown Interfacial Misfit GaSb/GaAs Heterostructures With and Without Te-Doped Interfaces. <i>IEEE Transactions on Electron Devices</i> , 2015, 62, 3980-3986.	1.6	5
483	Experimental evidences of quantum confined 2D indirect excitons in single barrier GaAs/AlAs/GaAs heterostructure using photocapacitance at room temperature. <i>Journal of Applied Physics</i> , 2018, 123, 044305.	1.1	5
484	Exciton localization and structural disorder of GaAs <sub>1-x</sub> Bi <sub>x</sub> /GaAs quantum wells grown by molecular beam epitaxy on (311)B GaAs substrates. <i>Semiconductor Science and Technology</i> , 2018, 33, 084002.	1.0	5
485	Thermal effects in thin conducting films on silica and alumina substrates under near-adiabatic conditions. <i>Journal Physics D: Applied Physics</i> , 1987, 20, 1451-1453.	1.3	4
486	Series addition of ballistic resistors. <i>Solid-State Electronics</i> , 1989, 32, 1303-1307.	0.8	4

#	ARTICLE	IF	CITATIONS
487	Photocreated holes and their effect on the luminescence, space charge and resonant tunnelling current in double barrier structures. <i>Superlattices and Microstructures</i> , 1990, 8, 195-200.	1.4	4
488	The effect of arsenic pressure on the diffusion-induced disordering of tin in AlAs-GaAs superlattices. <i>Journal of Materials Science: Materials in Electronics</i> , 1991, 2, 137-140.	1.1	4
489	Investigation of LO phonon emission by hot holes and the effective mass for hole tunnelling in GaAs/(AlGa)As single barrier structures. <i>Semiconductor Science and Technology</i> , 1992, 7, B446-B449.	1.0	4
490	Growth of p- and n-type GaAs/(AlGa)As double barrier resonant tunneling devices on (311)A and (111)B substrate orientations. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1992, 10, 2040.	1.6	4
491	Single electron tunnelling through a donor state in a gated resonant tunnelling device. <i>Surface Science</i> , 1992, 263, 438-441.	0.8	4
492	Effect of Si $\delta$ doping and growth temperature on the I(V) characteristics of molecular-beam epitaxially grown GaAs/(AlGa)As resonant tunneling devices. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1993, 11, 958.	1.6	4
493	Photoresistance imaging of quantum Hall devices. <i>Semiconductor Science and Technology</i> , 1994, 9, 2110-2115.	1.0	4
494	Magnetic-field-induced resonance in a triple-barrier resonant tunnelling diode. <i>Semiconductor Science and Technology</i> , 1994, 9, 493-496.	1.0	4
495	Electroreflectance studies of thin GaAs/AlGaAs quantum well structures with tunable 2DEG densities. <i>Superlattices and Microstructures</i> , 1994, 15, 119.	1.4	4
496	Modulated blue shift of the quantum well electroluminescence in a GaAs/AlAs superlattice resonant tunnelling device. <i>Solid-State Electronics</i> , 1994, 37, 843-846.	0.8	4
497	Two-dimensional electrons in a lateral magnetic superlattice. <i>Surface Science</i> , 1996, 361-362, 328-332.	0.8	4
498	Thermal stability of the silicon doping of GaAs grown on (111)A oriented substrates. <i>Applied Physics Letters</i> , 1996, 68, 652-654.	1.5	4
499	Two-dimensional electrons in a magnetic superlattice. <i>Solid-State Electronics</i> , 1996, 40, 217-220.	0.8	4
500	Tunneling spectroscopy of hole plasmons in a valence-band quantum well. <i>Physical Review B</i> , 1996, 54, R11106-R11109.	1.1	4
501	Investigation of Si as an n-type dopant in AlGaAs grown by molecular beam epitaxy on high index planes. <i>Semiconductor Science and Technology</i> , 1997, 12, 555-563.	1.0	4
502	High Magnetic Field Studies of Tunnelling Through X-Valley-Related Silicon Donor States in GaAs/AlAs Heterostructures. <i>Journal of the Physical Society of Japan</i> , 1997, 66, 2228-2231.	0.7	4
503	Milli-Kelvin magneto-transport studies of two-dimensional hole systems under illumination. <i>Solid State Communications</i> , 1997, 102, 53-58.	0.9	4
504	S-shaped current bistability in a bipolar resonant tunneling diode. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 1998, 2, 483-488.	1.3	4

#	ARTICLE	IF	CITATIONS
505	Effects on the resonant tunneling characteristics of a double-barrier diode of intentional and unintentional dopings in the quantum well. <i>Journal of Applied Physics</i> , 1999, 86, 1452-1455.	1.1	4
506	Quantum Hall effect breakdown of two dimensional hole gases. <i>Microelectronic Engineering</i> , 1999, 47, 35-37.	1.1	4
507	Hydrostatic pressure investigations of resonant tunnelling through X-minimum-related states in a single barrier GaAs/AlAs/GaAs heterostructure. <i>High Pressure Research</i> , 2000, 18, 63-67.	0.4	4
508	Electroluminescence from Individual InAs Self-Assembled Quantum Dots. <i>Physica Status Solidi A</i> , 2000, 178, 307-311.	1.7	4
509	Piezoelectric effects in InAs/GaAs(N11) self-assembled quantum dots. <i>Thin Solid Films</i> , 2000, 380, 198-200.	0.8	4
510	Ballistic phonon studies in the lowest Landau level. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2000, 6, 47-51.	1.3	4
511	Self-assembling of In(Ga)As/GaAs quantum dots on (N11) substrates: the (311)A case. <i>Micron</i> , 2000, 31, 309-313.	1.1	4
512	Piezoelectric Effects on the Electron-Hole Dipole in In <sub>0.5</sub> Ga <sub>0.5</sub> As/GaAs Self-Assembled Quantum Dots. <i>Physica Status Solidi (B): Basic Research</i> , 2001, 224, 37-40.	0.7	4
513	Anisotropy of electronic wave functions in self-assembled InAs dots embedded in the center of a GaAs quantum well studied by magnetotunneling spectroscopy. <i>JETP Letters</i> , 2001, 74, 41-45.	0.4	4
514	Magnetotransport studies of anisotropic scattering in GaAs/AlAs island superlattices. <i>Physical Review B</i> , 2002, 66, .	1.1	4
515	Effects of acoustic anisotropy and screening on the energy relaxation of hot electrons in heterojunctions and quantum wells. <i>Physical Review B</i> , 2002, 65, .	1.1	4
516	Controlling the electron tunneling through InAs self-assembled dots. <i>Journal of Applied Physics</i> , 2002, 91, 3474-3476.	1.1	4
517	Spin polarization of 2D electrons in the quantum Hall ferromagnet: evidence for a partially polarized state around filling factor one. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2002, 12, 12-15.	1.3	4
518	Quasi-ballistic transport of 2D electrons through magnetic barriers. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2002, 12, 229-232.	1.3	4
519	Morphological and optical anisotropy of quantum dots probed by magneto-tunneling and photoluminescence-polarization spectroscopy. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2002, 13, 170-173.	1.3	4
520	Linewidth broadening of excitonic luminescence from quantum wells in pulsed magnetic fields. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2002, 13, 349-352.	1.3	4
521	Electrical and optical properties of self-assembled quantum dots. <i>Microelectronics Journal</i> , 2002, 33, 313-318.	1.1	4
522	Probing the effective mass anisotropy of electrons in a GaAs/(AlGa)As quantum well. <i>Physical Review B</i> , 2003, 67, .	1.1	4

#	ARTICLE	IF	CITATIONS
523	Zeeman spectroscopy of Be impurity in GaAs. <i>Physica B: Condensed Matter</i> , 2004, 346-347, 483-487.	1.3	4
524	Modification of the Quantum Hall Effect by the Charge State of a Nearby Quantum Dot Layer. <i>Journal of the Physical Society of Japan</i> , 2006, 75, 114713.	0.7	4
525	Semiconductor terahertz emitters. , 2007, 6798, 225.		4
526	Magnetic-field-induced Fermi-edge singularity in the tunneling current through an InAs self-assembled quantum dot. <i>Journal of Experimental and Theoretical Physics</i> , 2007, 105, 152-154.	0.2	4
527	THE CIRCULAR PHOTO GALVANIC EFFECT IN TWO-DIMENSIONAL HOLE GASES IN PERPENDICULAR MAGNETIC FIELD. <i>International Journal of Modern Physics B</i> , 2009, 23, 2867-2871.	1.0	4
528	Laplace DLTS of molecular beam epitaxy GaAs grown on (100) and (211)B substrates. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009, 6, 2873-2875.	0.8	4
529	Carrier injection effects on exciton dynamics in GaAs/AlAs resonant-tunneling diodes. <i>Europhysics Letters</i> , 2009, 85, 67010.	0.7	4
530	Spin injection in n-type resonant tunneling diodes. <i>Nanoscale Research Letters</i> , 2012, 7, 592.	3.1	4
531	Effect of rapid thermal annealing on the electrical properties of dilute GaAsPN based diodes. <i>Semiconductor Science and Technology</i> , 2019, 34, 105009.	1.0	4
532	A Novel Parameter Identification Approach for $C-V$ Characteristics of Multi-Quantum Wells Schottky Diode Using Ant Lion Optimizer. <i>Russian Microelectronics</i> , 2019, 48, 428-434.	0.1	4
533	Investigation of the effects of GaAs substrate orientations on the electrical properties of sulfonated polyaniline based heterostructures. <i>Applied Surface Science</i> , 2020, 504, 144315.	3.1	4
534	The effect of strain and spatial Bi distribution on the band alignment of GaAsBi single quantum well structure. <i>Physica B: Condensed Matter</i> , 2021, 602, 412487.	1.3	4
535	Investigation of the effect of substrate orientation on the structural, electrical and optical properties of n-type GaAs $_{1-x}$ Bi $_x$ layers grown by Molecular Beam Epitaxy. <i>Journal of Alloys and Compounds</i> , 2021, 885, 161019.	2.8	4
536	INVESTIGATIONS OF THE NEGATIVE DIFFERENTIAL CONDUCTIVITY AND CURRENT BISTABILITY IN DOUBLE BARRIER n <sup>+</sup> /GaAs/(AlGa)As/GaAs/(AlGa)As/n <sup>+</sup> GaAs RESONANT TUNNELLING DEVICES USING HIGH MAGNETIC FIELDS. <i>Journal De Physique Colloque</i> , 1987, 48, C5-289-C5-292.	0.2	4
537	Annealing of GaAs/AlAs superlattices. <i>Journal of Materials Science: Materials in Electronics</i> , 1990, 1, 133-136.	1.1	3
538	Electronic processes in double barrier resonant tunneling structures investigated by optical spectroscopy. <i>Surface Science</i> , 1990, 229, 185-188.	0.8	3
539	Diffusion induced disorder in AlAs-GaAs superlattice by transition elements. <i>Journal of Electronic Materials</i> , 1991, 20, 649-652.	1.0	3
540	Measurement of the anisotropy of the hole dispersion curves in an AlAs/GaAs/AlAs quantum well grown on a (311)A orientated substrate. <i>Semiconductor Science and Technology</i> , 1992, 7, 1080-1084.	1.0	3



#	ARTICLE	IF	CITATIONS
541	An (AlGa)As/GaAs heterojunction bipolar transistor with a resonant-tunnelling collector. Semiconductor Science and Technology, 1994, 9, 1500-1503.	1.0	3
542	Reply to "Comment on "Anisotropy of the confined hole states in a (311)AlAs/GaAs/AlAs quantum-well system: Evidence for a camel's-back band structure". Physical Review B, 1994, 49, 8501-8501.	1.1	3
543	Surface acoustic wave absorption by edge magnetoplasmons in the 2DHG at a GaAs <sup>2</sup> AlGaAs heterojunction. Physica B: Condensed Matter, 1994, 194-196, 419-420.	1.3	3
544	Transport studies of the extreme quantum regime in 2D hole gas systems in pulsed magnetic fields. Physica B: Condensed Matter, 1994, 194-196, 1271-1272.	1.3	3
545	Proton implantation of resonant-tunnelling diode structures. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1995, 35, 376-381.	1.7	3
546	Phonon studies of the fractional quantum Hall effect. Physica B: Condensed Matter, 1995, 211, 400-403.	1.3	3
547	Growth and characterization of p-type As heterostructures grown on high-index GaAs surfaces. Thin Solid Films, 1995, 267, 106-113.	0.8	3
548	Resonant magnetotunnelling spectroscopy of a quantum loop. Solid-State Electronics, 1996, 40, 447-451.	0.8	3
549	The electronic transport through ion-implanted double-barrier diodes. Semiconductor Science and Technology, 1997, 12, 1282-1290.	1.0	3
550	Collective cyclotron modes in high-mobility two-dimensional hole systems in GaAs - (Ga, Al)As heterojunctions: II. Experiments at magnetic fields of up to forty Tesla. Journal of Physics Condensed Matter, 1997, 9, 4887-4896.	0.7	3
551	Multi-stage annealing of defects in ion-implanted double-barrier diodes. Semiconductor Science and Technology, 1997, 12, 1273-1281.	1.0	3
552	Transitions between Wannier-Stark States of a Superlattice at High Magnetic Field. Physica Status Solidi (B): Basic Research, 1997, 204, 374-377.	0.7	3
553	Photoluminescence investigation of p-type Si-doped AlGaAs grown by molecular beam epitaxy on (1 1) Tj ETQq1 1 0.784314 ggBT /Ov	0.7	3
554	Observation of a new type of giant magnetoresistance with possible sensor applications. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1998, 51, 216-218.	1.7	3
555	Mobility anisotropy of two-dimensional hole gases in (001)GaAs/Al <sub>0.5</sub> Ga <sub>0.5</sub> As heterostructures and the influence of uniaxial compression. Semiconductor Science and Technology, 1999, 14, 632-636.	1.0	3
556	Dissociation of indirect excitons: Discontinuity and bistability in the tunnel current of single-barrier heterostructures. Physical Review B, 1999, 60, 13302-13305.	1.1	3
557	Surface acoustic wave interactions with composite fermions and the acousto-electric effect. Physica B: Condensed Matter, 1999, 263-264, 205-207.	1.3	3
558	Observation of acoustic phonon Stokes and anti-Stokes peaks due to assisted tunnelling in a triple barrier structure. Physica B: Condensed Matter, 1999, 272, 171-174.	1.3	3



#	ARTICLE	IF	CITATIONS
559	New developments in superlattice transport: quenching of miniband conduction in high magnetic fields. <i>Microelectronic Engineering</i> , 1999, 47, 65-68.	1.1	3
560	Quasielastic light scattering in the near IR from photoexcited electron-hole plasma created in a GaAs layer with embedded InAs quantum dots. <i>Physics of the Solid State</i> , 1999, 41, 763-766.	0.2	3
561	The transition to chaos in a wide quantum well. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2000, 7, 735-739.	1.3	3
562	Observation of the interaction between Landau levels of different two-dimensional subbands in GaAs in a normal magnetic field. <i>JETP Letters</i> , 2000, 72, 476-479.	0.4	3
563	Acoustical plasma oscillations in photoexcited electron-hole plasma induced in GaAs layers embedded with InAs quantum dots. <i>Nanotechnology</i> , 2000, 11, 314-317.	1.3	3
564	Experimental observation of the negatively charged exciton states in high magnetic fields. <i>Nanotechnology</i> , 2000, 11, 281-285.	1.3	3
565	Piezoelectric Effects on Optical Properties and Carrier Kinetics of InAs/GaAs(N11) Self-Assembled Quantum Dots. <i>Physica Status Solidi (B): Basic Research</i> , 2001, 224, 111-114.	0.7	3
566	Probing the electronic properties of disordered two-dimensional systems by means of resonant tunnelling. <i>Nanotechnology</i> , 2001, 12, 491-495.	1.3	3
567	Bistability and discontinuity in the tunnel current of two-dimensional electron-hole layers. <i>Physical Review B</i> , 2001, 63, .	1.1	3
568	Phonon emission by optically pumped indium arsenide quantum dots in gallium arsenide. <i>Physica B: Condensed Matter</i> , 2002, 316-317, 198-201.	1.3	3
569	The acoustoelectric effect in double layer AlGaAs/GaAs 2D hole systems. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2002, 12, 462-465.	1.3	3
570	Exchange-enhanced energy shifts in the polarized photoluminescence of a two-dimensional hole system in the integer quantum Hall regime. <i>Physical Review B</i> , 2003, 68, .	1.1	3
571	Spatial mapping of the electron eigenfunctions in InAs self-assembled quantum dots by magnetotunnelling. <i>Nanotechnology</i> , 2003, 14, 16-19.	1.3	3
572	Carrier kinetics in a high-optically efficient quantum dot structure. <i>Semiconductor Science and Technology</i> , 2004, 19, S282-S284.	1.0	3
573	Observation of skyrmions in a two-dimensional hole system. <i>Physical Review B</i> , 2005, 71, .	1.1	3
574	Experimental observation of phase coherence in bilayer systems in the absence of a magnetic field. <i>JETP Letters</i> , 2006, 84, 209-213.	0.4	3
575	A TEM study of the evolution of InAs/GaAs self-assembled dots on (3 $\times$ 1)B GaAs with growth interruption. <i>Semiconductor Science and Technology</i> , 2007, 22, 168-170.	1.0	3
576	Monochromatic terahertz acoustic phonon emission from piezoelectric superlattices. <i>Journal of Physics: Conference Series</i> , 2007, 92, 012010.	0.3	3

#	ARTICLE	IF	CITATIONS
577	Magnetotunneling spectroscopy of polarons in a quantum well of a resonant-tunneling diode. Journal of Experimental and Theoretical Physics, 2010, 111, 220-224.	0.2	3
578	Intrinsic photoinduced anomalous Hall effect. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 940-943.	1.3	3
579	Magneto-optical investigation of two-dimensional gases in n-type resonant tunneling diodes. Semiconductor Science and Technology, 2012, 27, 015018.	1.0	3
580	Wetting-Layer-Pumped Continuous-Wave Surface-Emitting Quantum-Dot Laser. IEEE Photonics Technology Letters, 2012, 24, 37-39.	1.3	3
581	Circular polarization in n-type resonant tunneling diodes with Si delta-doping in the quantum well. , 2014, , .		3
582	Effect of post-growth annealing treatment on interfacial misfit GaSb/GaAs heterostructures. Journal of Crystal Growth, 2015, 424, 5-10.	0.7	3
583	Spin Polarization of Carriers in InGaAs Self-Assembled Quantum Rings Inserted in GaAs-AlGaAs Resonant Tunneling Devices. Journal of Electronic Materials, 2017, 46, 3851-3856.	1.0	3
584	Effects of nitrogen incorporation and thermal annealing on the optical and spin properties of GaPN dilute nitride alloys. Journal of Alloys and Compounds, 2020, 814, 152233.	2.8	3
585	Quantum chaology in semiconductor heterostructures. Physica Scripta, 1996, T68, 51-55.	1.2	3
586	Optimal identification of Be-doped Al <sub>0.29</sub> Ga <sub>0.71</sub> As Schottky diode parameters using Dragonfly Algorithm: A thermal effect study. Superlattices and Microstructures, 2021, 160, 107085.	1.4	3
587	TLM Modeling of Solder Joints in Semiconductor Devices. IEEE Transactions on Components, Hybrids and Manufacturing Technology, 1987, 10, 440-445.	0.4	2
588	Transmission-line matrix (TLM): a novel technique for modelling reaction kinetics. Journal of the Chemical Society, Faraday Transactions 2, 1987, 83, 843.	1.1	2
589	Transmission-line modelling of the Liesegang phenomenon. Journal of the Chemical Society, Faraday Transactions 2, 1987, 83, 837.	1.1	2
590	Investigation of asymmetric double barrier resonant tunneling structures based on (AlGa)As/GaAs. Journal of Crystal Growth, 1989, 95, 352-356.	0.7	2
591	Optical Spectroscopy of Double Barrier Resonant Tunneling Structures. Physica Scripta, 1991, T39, 271-277.	1.2	2
592	Voltage step response of resonant tunnel diodes. Superlattices and Microstructures, 1991, 10, 63-66.	1.4	2
593	Magnetic field-induced charge transfer to a GaAs/(Ga,Al)As quantum well interface studied by C(e,A0i) photoluminescence. Superlattices and Microstructures, 1991, 9, 319-321.	1.4	2
594	Effect of temperature on frequency limits of GaAs/AlGaAs resonant tunnel diodes. Electronics Letters, 1992, 28, 264.	0.5	2

#	ARTICLE	IF	CITATIONS
595	Annealing-induced dislocation loops in Si-doped GaAs-AlAs superlattices. <i>Journal of Materials Science: Materials in Electronics</i> , 1993, 4, 29.	1.1	2
596	Fluxon-resolved studies of high-T <sub>c</sub> superconducting films. <i>Physica C: Superconductivity and Its Applications</i> , 1994, 235-240, 3137-3138.	0.6	2
597	Phonon measurements of the energy gap in the fractional quantum Hall state. <i>Surface Science</i> , 1994, 305, 87-90.	0.8	2
598	A novel approach in fabrication and study of laterally quantum-confined resonant tunnelling diodes. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1995, 35, 192-197.	1.7	2
599	Studies of the extreme quantum limit of 2D hole systems. <i>Physica B: Condensed Matter</i> , 1995, 211, 417-419.	1.3	2
600	$\sigma_{xx}$ Mixing studied by electroluminescence spectroscopy under hydrostatic pressure in a GaAs/AlAs p-i-n superlattice resonant tunnelling device. <i>Journal of Physics and Chemistry of Solids</i> , 1995, 56, 403-406.	1.9	2
601	Introduction to the 1st International Workshop on growth, characterization and exploitation of epitaxial III-V compound semiconductor on novel index surfaces. <i>Microelectronics Journal</i> , 1995, 26, 737-738.	1.1	2
602	Classical Edge Magnetoplasmons in GaAs/AlGaAs Two-Dimensional Hole System. <i>Japanese Journal of Applied Physics</i> , 1995, 34, L69-L71.	0.8	2
603	Moderate-dose proton implantation through double-barrier structures. <i>Electronics Letters</i> , 1996, 32, 140.	0.5	2
604	Phonon-assisted tunnelling in GaAs/(AlGa)As resonant tunnelling devices. <i>Physica B: Condensed Matter</i> , 1996, 219-220, 19-21.	1.3	2
605	The acousto-electric effect in the 2-D hole system using SAW. <i>Physica B: Condensed Matter</i> , 1996, 219-220, 22-24.	1.3	2
606	Skyrmion Excitations in a Two-Dimensional Electron Gas under Hydrostatic Pressure. <i>Physica Status Solidi (B): Basic Research</i> , 1996, 198, 259-266.	0.7	2
607	Is the be incorporation the same in (311)A and (100) AlGaAs?. <i>Microelectronics Journal</i> , 1997, 28, 993-998.	1.1	2
608	PLE studies of two-dimensional hole systems in the quantum Hall regime. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 1997, 1, 116-119.	1.3	2
609	Observation of giant magnetoresistances in hybrid semiconductor/ferromagnetic devices. <i>Journal of Magnetism and Magnetic Materials</i> , 1998, 177-181, 898-899.	1.0	2
610	Far-infrared laser photoconductivity of n-GaAs multiple quantum wells in a pulsed magnetic field. <i>Physica B: Condensed Matter</i> , 1998, 246-247, 290-293.	1.3	2
611	Angle-resolved ballistic phonon absorption spectroscopy in the lowest Landau level. <i>Physica B: Condensed Matter</i> , 1998, 256-258, 36-42.	1.3	2
612	Polaron pinning effects in superlattices at high electric and magnetic fields. <i>Physica B: Condensed Matter</i> , 1998, 256-258, 540-543.	1.3	2

#	ARTICLE	IF	CITATIONS
613	A study of miniband conduction in Wannier- $\tilde{C}$ Stark superlattices at high magnetic fields. <i>Physica B: Condensed Matter</i> , 1998, 256-258, 544-547.	1.3	2
614	Excitonic and free-carrier recombination of a two-dimensional electron gas in high magnetic fields. <i>Physica B: Condensed Matter</i> , 1998, 256-258, 327-330.	1.3	2
615	High index surfaces grow novel devices. <i>III-Vs Review</i> , 1998, 11, 48-52.	0.1	2
616	Time-resolved imaging of the boundary excitations of a two-dimensional electron gas in a magnetic field. <i>Physical Review B</i> , 1999, 60, R16307-R16310.	1.1	2
617	The transition to chaos for hot electrons in a wide quantum well. <i>Physica B: Condensed Matter</i> , 1999, 272, 163-166.	1.3	2
618	In <sub>0.5</sub> Ga <sub>0.5</sub> As quantum dot lasers grown on (100) and (311)B GaAs substrates. <i>Journal of Crystal Growth</i> , 1999, 201-202, 1139-1142.	0.7	2
619	Probing the electronic density of states in semiconductor quantum wires using nonequilibrium acoustic phonons. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2000, 6, 522-525.	1.3	2
620	Energy dependence of the quasiparticle lifetime in a 2DES. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2000, 6, 327-330.	1.3	2
621	Carrier hopping in InAs/Al <sub>y</sub> Ga <sub>1-y</sub> As quantum dot heterostructures: effects on optical and laser properties. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2000, 7, 452-455.	1.3	2
622	Phonon-induced conductivity of ballistic quantum wires. <i>Physical Review B</i> , 2000, 61, R16311-R16314.	1.1	2
623	Surface acoustic wave study of a double layer AlGaAs/GaAs 2D hole system. <i>Physica B: Condensed Matter</i> , 2001, 298, 70-73.	1.3	2
624	Chaos in quantum wells and analogous optical systems. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2001, 11, 114-117.	1.3	2
625	Surface acoustic wave attenuation by the localized states of a two-dimensional carrier system in a magnetic field. <i>Semiconductor Science and Technology</i> , 2001, 16, 136-139.	1.0	2
626	FURTHER EVIDENCE FOR A COLLAPSE OF THE EXCHANGE-ENHANCED SPIN SPLITTING IN TWO DIMENSIONAL SYSTEMS. <i>International Journal of Modern Physics B</i> , 2004, 18, 3597-3602.	1.0	2
627	Measurements of phonons generated by optical excitation of GaAs, using a superlattice phonon spectrometer. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2004, 1, 2783-2786.	0.8	2
628	Self-organised criticality in the quantum Hall effect. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2004, 22, 210-213.	1.3	2
629	Resistance noise scaling in a dilute two-dimensional hole system in GaAs. , 2004, , .		2
630	Electrical characterisation of (Ga,Mn,Cr)As thin films grown by molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2005, 278, 695-698.	0.7	2

#	ARTICLE	IF	CITATIONS
631	Transport properties of gated sub-micron mesas incorporating InAs self-assembled quantum dots that conduct near zero bias. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2005, 26, 482-485.	1.3	2
632	Phonon-assisted tunneling in a superlattice in an applied magnetic field. <i>Physical Review B</i> , 2009, 80, .	1.1	2
633	Measurement of a large hole g-factor in two-dimensional hole gases. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2010, 42, 964-966.	1.3	2
634	Growth and characterization of ingan for photovoltaic devices. , 2010, , .		2
635	Circular polarization in a non-magnetic resonant tunneling device. <i>Nanoscale Research Letters</i> , 2011, 6, 101.	3.1	2
636	Spin effects in InAs self-assembled quantum dots. <i>Nanoscale Research Letters</i> , 2011, 6, 115.	3.1	2
637	Optical and electrical control of spin polarization of two-dimensional hole gases in p-type resonant tunnelling devices. <i>Journal Physics D: Applied Physics</i> , 2013, 46, 505313.	1.3	2
638	Visualization of wave function of quantum dot at Fermi-edge singularity regime. <i>Journal of Physics: Conference Series</i> , 2013, 456, 012024.	0.3	2
639	A comparative photoluminescence study on Mn-Free GaAs/AlAs and Mn-containing Ga <sub>1-x</sub> Mn <sub>x</sub> As/AlAs quantum wells (QWs) grown on various orientations by MBE. <i>Philosophical Magazine</i> , 2016, 96, 223-229.	0.7	2
640	Piezoelectric Response to Coherent Longitudinal and Transverse Acoustic Phonons in a Semiconductor Schottky Diode. <i>Physical Review Applied</i> , 2017, 7, .	1.5	2
641	Structural and optical properties of diluted magnetic $\text{Ga}_{1-x}\text{Mn}_x$ . <i>Bulletin of Materials Science</i> , 2017, 40, 1355-1359.	0.8	2
642	Simulation of p-type Schottky Diode Based on Al <sub>0.29</sub> Ga <sub>0.71</sub> As with Titanium/Gold Schottky Contact. , 2018, , .		2
643	Role of interface potential barrier, Auger recombination and temporal coherence in In <sub>0.5</sub> Ga <sub>0.5</sub> As/GaAs quantum dot-based p-i-n light emitting diodes. <i>Journal Physics D: Applied Physics</i> , 2019, 52, 095102.	1.3	2
644	The Role of Defects on the Performance of Quantum Dot Intermediate Band Solar Cells. <i>IEEE Journal of Photovoltaics</i> , 2021, 11, 1022-1031.	1.5	2
645	I-V-T measurements on GaAs/AlGaAs heterojunctions interpreted on the basis of thermally assisted tunneling. <i>EPJ Applied Physics</i> , 2000, 9, 131-136.	0.3	2
646	Comparative study of various methods for extraction of multi- quantum wells Schottky diode parameters. <i>Journal of Semiconductors</i> , 2020, 41, 102401.	2.0	2
647	Schottky contact diameter effect on the electrical properties and interface states of Ti/Au/p-AlGaAs/GaAs/Au/Ni/Au Be-doped p-type MBE Schottky diodes. <i>Semiconductor Science and Technology</i> , 0, , .	1.0	2
648	Temperature and angular dependence of magnetoresistance oscillations in a 2deg subjected to a periodic potential. <i>Physica B: Condensed Matter</i> , 1990, 165-166, 867-868.	1.3	1

#	ARTICLE	IF	CITATIONS
649	Acoustic phonon scattering by a 2-dimensional electron gas. <i>Physica B: Condensed Matter</i> , 1990, 165-166, 873-874.	1.3	1
650	Sulphur diffusion in GaAs-AlAs superlattices. <i>Optical and Quantum Electronics</i> , 1991, 23, S813-S821.	1.5	1
651	Vertical transport in a GaAs/(Ga,Al)As superlattice containing an enlarged quantum well studied by photoluminescence in high in-plane magnetic fields. <i>Semiconductor Science and Technology</i> , 1992, 7, 676-680.	1.0	1
652	Semiconductor lasers: An overview part II. <i>III-Vs Review</i> , 1993, 6, 50-53.	0.1	1
653	High magnetic field studies of the confined hole states in quantum wells grown on novel substrate orientations. <i>Physica B: Condensed Matter</i> , 1993, 184, 285-288.	1.3	1
654	Hierarchy of periodic orbits and associated energy level clusters in a quantum well in the regime of classical chaos. <i>Superlattices and Microstructures</i> , 1994, 15, 287.	1.4	1
655	Discrete electroluminescence lines in sub-micron p-i-n resonant tunnelling diodes. <i>Superlattices and Microstructures</i> , 1994, 16, 169.	1.4	1
656	An overview of narrow bandgap semiconductors. <i>III-Vs Review</i> , 1994, 7, 44-49.	0.1	1
657	Prospects for the future of resonant tunnelling devices " Part 1. <i>III-Vs Review</i> , 1994, 7, 33-36.	0.1	1
658	Optoelectronic materials and devices. <i>Microelectronics Journal</i> , 1994, 25, 607-608.	1.1	1
659	<title>Observation of the Mahan exciton using electroreflectance spectroscopy of a quantum well structure</title>. , 1994, 2139, 2.		1
660	Comparison of the quantum confined stark effect for (100)- and (311)A-oriented GaAs/AlGaAs quantum wells using electroreflectance spectroscopy. <i>Superlattices and Microstructures</i> , 1995, 17, 401.	1.4	1
661	Universal behaviour of the thermoelectric power of composite fermions. <i>Surface Science</i> , 1996, 361-362, 46-49.	0.8	1
662	Creation and annihilation of positively and negatively charged excitons in GaAs quantum wells. <i>Surface Science</i> , 1996, 361-362, 447-450.	0.8	1
663	Effective mass anisotropy and many-body effects in 2D GaAs/(Ga,Al)As hole gases observed in very high magnetic fields: comparison of theory and experiment. <i>Surface Science</i> , 1996, 361-362, 464-467.	0.8	1
664	Phonon spectroscopy of the fractional quantum Hall effect. <i>Physica Scripta</i> , 1996, T66, 163-166.	1.2	1
665	Molecular beam epitaxy from research to mass-production " Part II. <i>III-Vs Review</i> , 1996, 9, 33-36.	0.1	1
666	Tuning the inter-subband tunnelling and universal conductance fluctuations with an in-plane magnetic field in the "quantum transport regime"™. <i>Superlattices and Microstructures</i> , 1997, 22, 307-311.	1.4	1

#	ARTICLE	IF	CITATIONS
667	Resonant tunnelling of holes in double barrier heterostructures grown by MBE on (1 1 0) oriented GaAs substrates. Journal of Crystal Growth, 1997, 175-176, 919-923.	0.7	1
668	Pressure dependence of the cyclotron resonance modes in high mobility two-dimensional hole systems in GaAs (Ga,Al)As heterojunctions. Physica B: Condensed Matter, 1998, 256-258, 359-362.	1.3	1
669	Direct measurements of the electron-acoustic phonon interaction in GaAs quantum wire structures. Physica B: Condensed Matter, 1999, 263-264, 170-174.	1.3	1
670	Angle-resolved ballistic phonon absorption spectroscopy in the lowest Landau level. Physica B: Condensed Matter, 1999, 263-264, 196-198.	1.3	1
671	Effect of nonequilibrium phonons on the tunnel current in superlattices. Superlattices and Microstructures, 1999, 25, 459-462.	1.4	1
672	Hot electron spectroscopy of carrier relaxation within indirect AlAs tunnel barriers. Applied Physics Letters, 1999, 75, 3539-3541.	1.5	1
673	Direct observation of vortex lattice melting in Bi/sub 2/Sr/sub 2/CaCu/sub 2/O/sub 8+ $\delta$ / single crystals. IEEE Transactions on Applied Superconductivity, 1999, 9, 1820-1823.	1.1	1
674	Phase coherence and size effects in double quantum well mesoscopic wires. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 6, 672-675.	1.3	1
675	Magneto-Tunnelling Spectroscopy for Spatial Mapping of Orbital Wavefunctions of the Ground and Excited Electronic States in Self-Assembled Quantum Dots. Physica Status Solidi (B): Basic Research, 2001, 224, 715-722.	0.7	1
676	High Pressure as a Tool to Study Electron Localization. Physica Status Solidi (B): Basic Research, 2001, 223, 555-559.	0.7	1
677	Optical Properties and Laser Applications of (InGa)As/(AlGa)As Self-Assembled Quantum Dots. Japanese Journal of Applied Physics, 2001, 40, 2077-2079.	0.8	1
678	Magnetotunneling spectroscopy imaging of electron wave functions in self-assembled InAs quantum dots. Physics-Uspexhi, 2001, 44, 1299-1301.	0.8	1
679	<title>Inelastic inter-valence-band scattering of photoexcited holes in quantum dot structures</title>. , 2002, , .		1
680	Magnetic waveguiding in tilted magnetic fields. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 12, 220-223.	1.3	1
681	Mapping the wave functions in quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 12, 794-801.	1.3	1
682	Nonlinear hole transport through a submicron-size channel. Applied Physics Letters, 2003, 82, 925-927.	1.5	1
683	Electrically pumped terahertz SASER device using a weakly coupled AlAs/GaAs superlattice as the gain medium. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 2682-2685.	0.8	1
684	Temperature-dependent high-current breakdown of the quantum Hall effect. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 22, 201-204.	1.3	1



#	ARTICLE	IF	CITATIONS
685	Breakdown of the Quantum Hall Effects in Hole Systems at High Induced Currents. AIP Conference Proceedings, 2005, , .	0.3	1
686	Quasiballistic transport of hot holes in GaAs submicron channels. Applied Physics Letters, 2005, 86, 042101.	1.5	1
687	Pspice resonant tunneling diode models and application circuits. International Journal of Electronics, 2005, 92, 131-142.	0.9	1
688	Spin dynamics in (110)-oriented quantum wells. Microelectronics Journal, 2006, 37, 1486-1489.	1.1	1
689	Demonstration of monochromatic terahertz acoustic phonon generation in superlattices under hopping transport. AIP Conference Proceedings, 2007, , .	0.3	1
690	Optical characterization of (In,Ga)(As,N) thin films grown by molecular beam epitaxy on non-(100) GaAs substrates. Journal of Crystal Growth, 2007, 301-302, 552-555.	0.7	1
691	One-electron spin-dependent transport in split-gate structures containing self-organized InAs quantum dots. Journal of Experimental and Theoretical Physics, 2007, 105, 145-148.	0.2	1
692	Observation of the low-temperature peak in the interlayer tunneling conductance in bilayer electron systems in the absence of the magnetic field. Journal of Experimental and Theoretical Physics, 2007, 105, 177-180.	0.2	1
693	Antenna-coupled direct detector for millimetre and submillimetre astronomy based on 2D electron gas in semiconducting heterostructure. Proceedings of SPIE, 2008, , .	0.8	1
694	Preliminary comparison of ballistic electron emission spectroscopy measurements on InAs quantum dots in a GaAs/AlGaAs heterostructure grown by MBE and MOVPE. Microelectronics Journal, 2009, 40, 496-498.	1.1	1
695	Temperature dependence of the photoluminescence of self-assembled InAs/GaAs quantum dots studied in high magnetic fields. Microelectronics Journal, 2009, 40, 486-488.	1.1	1
696	Optical Measurement Of The Rashba Coefficient In GaAs/AlGaAs Quantum Wells. , 2010, , .		1
697	Rashba Conduction Band Spin-Splitting for Asymmetric Quantum Well Potentials. Journal of Superconductivity and Novel Magnetism, 2010, 23, 157-159.	0.8	1
698	Temperature dependence of dark current in a p <sup>+</sup> -i <sup>n</sup> photodiode incorporating a resonant tunneling structure. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 210-214.	0.8	1
699	Observation of the anomalous temperature dependence of resonance tunneling through zero-dimensional states in a quantum well with dynamic coulomb interaction between the tunneling channels. JETP Letters, 2012, 96, 529-535.	0.4	1
700	Deep level transient spectroscopy characterisation of defects in AlGaIn/Si dual-band (UV/IR) detectors grown by MBE. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 101-104.	0.8	1
701	Voltage controlled electron spin dynamics in resonant tunnelling devices. Journal Physics D: Applied Physics, 2014, 47, 165102.	1.3	1
702	Structural and elastic stabilities of InN in both B4 and B1 phases under high pressure using density-functional perturbation theory. Journal of Alloys and Compounds, 2015, 650, 450-457.	2.8	1



#	ARTICLE	IF	CITATIONS
703	$\beta$ -rays irradiation effects on dielectric properties of Ti/Au/GaAsN Schottky diodes with 1.2%N. Radiation Physics and Chemistry, 2018, 147, 13-17.	1.4	1
704	Piezoelectric Effects on the Electron-Hole Dipole in In <sub>0.5</sub> Ga <sub>0.5</sub> As/GaAs Self-Assembled Quantum Dots. , 2001, 224, 37.		1
705	Fine Structure of the Localized Emission from GaInNAs Layers Studied by Micro-Photoluminescence. Acta Physica Polonica A, 2009, 116, 930-932.	0.2	1
706	2D Electron Gas in Non-Uniform Magnetic Fields. Acta Physica Polonica A, 2000, 98, 217-230.	0.2	1
707	Phonon Interaction on a Single Quantum Dot Emission Line. , 2009, , .		1
708	High-Pressure Magnetotransport Measurements of Resonant Tunnelling via X-Minimum Related States in AlAs Barrier. Acta Physica Polonica A, 2001, 100, 403-408.	0.2	1
709	Capacitance Spectroscopy of Single-Barrier GaAs/AlAs/GaAs Structures Containing InAs Quantum Dots. Acta Physica Polonica A, 1998, 94, 245-249.	0.2	1
710	Nonlinear thermal effects in thin-film conductors on insulating substrates. Electronics Letters, 1987, 23, 552-554.	0.5	0
711	Deep levels in GaAs/AlGaAs multi-quantum well structures. Journal of Materials Science: Materials in Electronics, 1990, 1, 75-78.	1.1	0
712	Effects of interface donors on far infrared photoresponse at cyclotron resonance in a (AlGa)As/GaAs heterojunction. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1990, 8, 783.	1.6	0
713	HIGH RESOLUTION TEM-CL FROM THE CROSS-SECTIONAL SPECIMENS OF GaAs/AlGaAs QWs. European Physical Journal Special Topics, 1991, 01, C6-125-C6-130.	0.2	0
714	Investigation of a double barrier resonant tunnelling structure which incorporates an optical window layer in the top contact. Journal of Crystal Growth, 1991, 111, 1089-1094.	0.7	0
715	<title>New all-optical reflection modulator using a resonant hetero-nipi Bragg reflector</title>. , 1992, 1675, 485.		0
716	Wide bandgap electronic materials part I. III-Vs Review, 1992, 5, 54-56.	0.1	0
717	Wide bandgap electronic materials part II. III-Vs Review, 1992, 5, 55-57.	0.1	0
718	A new role for the scanning tunnelling microscope. III-Vs Review, 1993, 6, 58-62.	0.1	0
719	Semiconductor lasers: An overview part I. III-Vs Review, 1993, 6, 54-57.	0.1	0
720	<title>Investigation of doped multiple quantum well structures using modulation spectroscopy</title>. , 1994, 2141, 80.		0

#	ARTICLE	IF	CITATIONS
721	The pinning potential at single flux vortices investigated using sub-micron hall probes. Physica B: Condensed Matter, 1994, 194-196, 1899-1900.	1.3	0
722	Prospects for the future of resonant tunnelling devices - Part 2. III-Vs Review, 1994, 7, 50-52.	0.1	0
723	The physics and technology of low dimensional structures. Microelectronics Journal, 1994, 25, xxix-xlvi.	1.1	0
724	Electroluminescence in p-i-n double-barrier resonant tunnelling structures. Microelectronics Journal, 1994, 25, 741-746.	1.1	0
725	Cretion and annihilation of negatively charged excitons in GaAs quantum wells. Nuovo Cimento Della Societa Italiana Di Fisica D - Condensed Matter, Atomic, Molecular and Chemical Physics, Biophysics, 1995, 17, 1395-1400.	0.4	0
726	Resonant magnetotunneling via quantum confined states. Physica B: Condensed Matter, 1995, 211, 423-429.	1.3	0
727	First international workshop on growth, characterization and exploitation of epitaxial III-V compound semiconductors on novel index surfaces, Trento (Italy), 4-7 December 1994. Microelectronics Journal, 1995, 26, xix-xxiii.	1.1	0
728	Current-voltage nonlinearity in the multiquantum well nin modulator structure. Electronics Letters, 1995, 31, 2040-2041.	0.5	0
729	Resonant tunnelling through D <sup>+</sup> states. Surface Science, 1996, 361-362, 247-250.	0.8	0
730	Even denominator filling factors in the thermoelectric power of a 2DEG. European Physical Journal D, 1996, 46, 2461-2462.	0.4	0
731	Imaging the edge channel structure in a quantum Hall device. European Physical Journal D, 1996, 46, 2463-2464.	0.4	0
732	Collective excitations of the fractional quantum Hall effect. Physica B: Condensed Matter, 1996, 219-220, 5-8.	1.3	0
733	Far infrared reflectivity of a GaAs/Al <sub>0.33</sub> Ga <sub>0.67</sub> As multiple quantum well structure. Microelectronics Journal, 1996, 27, 87-92.	1.1	0
734	Low dimensional structures and devices: epitaxial deposition techniques and materials systems. Microelectronics Journal, 1996, 27, 253-255.	1.1	0
735	Land of ancient myths, super-microchips & quantum devices part II. III-Vs Review, 1996, 9, 64-67.	0.1	0
736	Optical and microscopic properties of In <sub>0.5</sub> Ga <sub>0.5</sub> As/GaAs highly strained heterostructures. , 1997, , .		0
737	Scanning Hall Probe Microscopy Of Ferromagnetic Structures. , 0, , .		0
738	MBE growth and physics of strongly coupled p-type double quantum wells showing correlated $\nu = 1$ quantum Hall state. Journal of Crystal Growth, 1997, 175-176, 1138-1143.	0.7	0

#	ARTICLE	IF	CITATIONS
739	Introduction to the 2nd international workshop on growth, characterization and exploitation of epitaxial compound semiconductor on novel index surfaces (NIS '96). <i>Microelectronics Journal</i> , 1997, 28, 703-705.	1.1	0
740	Asahi chemical puts faith in Hall sensors. <i>III-Vs Review</i> , 1997, 10, 32-36.	0.1	0
741	EMC provides extensive electronic materials update. <i>III-Vs Review</i> , 1997, 10, 49-50.	0.1	0
742	Atom technology at Nair. <i>III-Vs Review</i> , 1997, 10, 34-37.	0.1	0
743	Low dimensional structures and devices: micro- and nano-technology. <i>Microelectronics Journal</i> , 1997, 28, 367-370.	1.1	0
744	Influence of the buffer layer on the FIR reflectivity spectra of a thick superlattice. <i>Superlattices and Microstructures</i> , 1997, 21, 143-150.	1.4	0
745	Spin-dependent holed delocalization enhancement by bandfilling effects in degenerate asymmetric double quantum wells. <i>Superlattices and Microstructures</i> , 1997, 21, 217-222.	1.4	0
746	MBE growth and magnetotunnelling transport properties of a single GaAs/AlAs/GaAs barrier incorporating InAs quantum dots. <i>Journal of Crystal Growth</i> , 1997, 175-176, 782-786.	0.7	0
747	Phonon scattering from self-aligned InAs quantum dots in GaAs. <i>Microelectronic Engineering</i> , 1998, 43-44, 25-29.	1.1	0
748	Novel characteristics of self assembled InAs quantum dots grown on (311)A GaAs. <i>Microelectronic Engineering</i> , 1998, 43-44, 45-49.	1.1	0
749	Photoluminescence of self organised InAs/GaAs quantum dots grown on (N11)B surfaces. <i>Microelectronic Engineering</i> , 1998, 43-44, 67-70.	1.1	0
750	Hybrid stable-chaotic states in coupled quantum well stadia. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 1998, 2, 287-290.	1.3	0
751	Optical and Resonant Tunnelling Spectroscopy of Self-Assembled Quantum Dot Systems. <i>Japanese Journal of Applied Physics</i> , 1999, 38, 535-538.	0.8	0
752	Saw attenuation by the localised states of a 2D carrier system in a magnetic field. <i>Physica B: Condensed Matter</i> , 1999, 263-264, 214-216.	1.3	0
753	Carrier dynamics in double barrier diodes incorporating quantum dots. <i>Physica B: Condensed Matter</i> , 1999, 272, 21-23.	1.3	0
754	Relaxation of electrons within AlAs barriers studied by hot electron spectroscopy. <i>Physica B: Condensed Matter</i> , 1999, 272, 153-156.	1.3	0
755	Highly nonlinear capacitance in quantum well/barrier heterostructures: application to harmonic multiplication at terahertz frequency. , 1999, , .		0
756	Dissociation of indirect excitons: discontinuity and bistability in the tunnel current of 2D electron-hole layers. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2000, 6, 832-835.	1.3	0

#	ARTICLE	IF	CITATIONS
757	III-Vs advance on silicon. III-Vs Review, 2000, 13, 34-38.	0.1	0
758	Magnetotunnelling spectroscopy for probing the electron wave functions in self-assembled quantum dots. Physica B: Condensed Matter, 2001, 298, 254-259.	1.3	0
759	Anti-crossing of Landau levels of different two-dimensional subbands in GaAs in normal magnetic field. Physica B: Condensed Matter, 2001, 298, 359-363.	1.3	0
760	Emission energy and polarization tuning of InAs/GaAs self-assembled dots by growth interruption. , 0, , .		0
761	Control of the coalescence phenomena in InAs/GaAs quantum dots by using high-index planes. , 0, , .		0
762	InAs/GaAs quantum dot formation studied by magneto-photoluminescence spectroscopy. , 0, , .		0
763	<title>Effective mass anisotropy of T-electrons in GaAs/AlGaAs quantum well with InAs layer</title>. , 2002, , .		0
764	<title>Magneto-tunnelling spectroscopy of the electron states in the quantum well with embedded self assembled quantum dots: studies in magnetic field up to 28 T</title>. , 2002, , .		0
765	<title>Tunnel gaps in the two-dimensional electron system in a magnetic field</title>. , 2002, , .		0
766	Resistance fluctuations in a low density 2D hole gas in GaAs. European Physical Journal Special Topics, 2002, 12, 263-264.	0.2	0
767	Ballistic phonon interactions with the fractional quantum Hall effect liquid. Physica B: Condensed Matter, 2002, 316-317, 101-106.	1.3	0
768	Surface acoustic wave comparison of single and double layer AlGaAs/GaAs 2D hole systems. Physica B: Condensed Matter, 2002, 316-317, 219-222.	1.3	0
769	The spin polarization of 2D electrons in the region $1 < \nu < 2$ and a determination of the Composite Fermion mass. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 12, 93-96.	1.3	0
770	Magnetoresistance oscillations in a periodic magnetic field due to internal Landau band structure. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 12, 212-215.	1.3	0
771	Magnetophotoluminescence of positively-charged excitons in GaAs quantum wells. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 12, 516-519.	1.3	0
772	Magnetic field induced linear Coulomb gap in tunnelling between disordered two-dimensional electron systems. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 12, 300-303.	1.3	0
773	Miniband magneto-transport in GaAs/AlAs island superlattices. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 13, 786-789.	1.3	0
774	Influence of intrinsic internal field on recombination kinetics of high coverage (N11) InAs/GaAs quantum dots. European Physical Journal B, 2002, 27, 75-78.	0.6	0

#	ARTICLE	IF	CITATIONS
775	Magneto-photoluminescence studies of the influence of substrate orientation on the growth of InAs/GaAs quantum dots. <i>Journal of Crystal Growth</i> , 2003, 251, 186-191.	0.7	0
776	A grazing incidence small angle X-ray scattering study of the effect of growth interrupt on the structure of InAs quantum dots. , 0, , .		0
777	Preface for NANO' 2003 proceedings. <i>Microelectronics Journal</i> , 2004, 35, 1.	1.1	0
778	Generation and propagation of THz monochromatic acoustic phonons in gallium arsenide. , 2004, , .		0
779	Generation of transverse acoustic phonons in a GaAs/AlAs superlattice by ultrafast optical excitation. <i>Semiconductor Science and Technology</i> , 2004, 19, S270-S272.	1.0	0
780	Charge buildup effects in asymmetric p-type resonant tunneling diodes. <i>Microelectronics Journal</i> , 2005, 36, 356-358.	1.1	0
781	The resonant tunneling of holes through double-barrier structures with InAs QDs at the center of a GaAs quantum well. <i>Semiconductors</i> , 2005, 39, 543-546.	0.2	0
782	Coulomb Oscillations of the Current through Spin-Nondegenerate p States of InAs Quantum Dots. <i>JETP Letters</i> , 2005, 82, 526.	0.4	0
783	Observation of current resonances due to enhanced electron transport through stochastic webs in superlattices. <i>AIP Conference Proceedings</i> , 2005, , .	0.3	0
784	1/f Noise In Low Density Two-Dimensional Hole Systems In GaAs. <i>AIP Conference Proceedings</i> , 2005, , .	0.3	0
785	Microwave resonance susceptibility of a two-dimensional hole system in a weak random potential. <i>Physical Review B</i> , 2005, 71, .	1.1	0
786	High sensitivity terahertz detector using two-dimensional electron gas absorber and tunnel junction contacts as a thermometer. , 2006, , .		0
787	Magnetotunneling spectroscopy of ring-shaped (InGa)As quantum dots: Evidence of excited states with 2pz character. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2006, 32, 57-60.	1.3	0
788	Anomalous quantum Hall effect induced by nearby quantum dots. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2006, 34, 148-151.	1.3	0
789	Sixth International Workshop on Epitaxial Semiconductors on Patterned Substrates and Novel Index Surfaces (ESPS-NIS 2006). <i>Microelectronics Journal</i> , 2006, 37, 1425-1426.	1.1	0
790	INFLUENCE OF NEARBY QD LAYER ON 2DES IN QUANTUM HALL REGIME. <i>International Journal of Modern Physics B</i> , 2007, 21, 1445-1449.	1.0	0
791	Recent progress in self-assembled quantum-dot optical devices. <i>Proceedings of SPIE</i> , 2007, , .	0.8	0
792	Coherent phonons in a doped GaAs/AlAs superlattice. <i>Journal of Physics: Conference Series</i> , 2007, 92, 012014.	0.3	0

#	ARTICLE	IF	CITATIONS
793	Spin Relaxation in 2D Electron Gases in the Strong Scattering Regime. AIP Conference Proceedings, 2007, , .	0.3	0
794	Coherent Oscillatory Spin-Dynamics in High-Mobility 2D Electron Gases. AIP Conference Proceedings, 2007, , .	0.3	0
795	Magnetic-field-induced Stoner transition in a quantum Hall ferromagnet at high filling factors. AIP Conference Proceedings, 2007, , .	0.3	0
796	Bose condensation of excitons in two-layer electronic systems in the absence of magnetic field. Bulletin of the Russian Academy of Sciences: Physics, 2007, 71, 1120-1123.	0.1	0
797	Single-electron spin-dependent transport in split-gate structures containing self-assembled quantum dots. Bulletin of the Russian Academy of Sciences: Physics, 2007, 71, 1124-1126.	0.1	0
798	Magnetic-field-induced Fermi-edge singularity in the tunnelling current through a self-assembled InAs quantum dot. Bulletin of the Russian Academy of Sciences: Physics, 2007, 71, 1127-1129.	0.1	0
799	Determination of the Landau level shape via the transition to the spin polarized state in the integer quantum Hall effect. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 1200-1201.	1.3	0
800	MAGNETIC FIELD DEPENDENCE OF MANY-BODY ENHANCED ELECTRON TUNNELLING THROUGH A QUANTUM DOT. International Journal of Modern Physics B, 2009, 23, 2974-2978.	1.0	0
801	Effect of Charge State in Nearby Quantum Dots on Quantum Hall Systems. Journal of Low Temperature Physics, 2010, 159, 234-237.	0.6	0
802	Cyclotron study of 2DES incorporating QD layer. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 915-917.	1.3	0
803	Photoinduced Anomalous Hall Effect in 2-Dimensional Hole Gases. , 2010, , .		0
804	The Absence Of The Rashba Spin-Splitting In Undoped Asymmetric Quantum Wells. , 2010, , .		0
805	Cyclotron resonance of two-dimensional electron system affected by neighboring quantum dot layer. Applied Physics Letters, 2010, 96, 193110.	1.5	0
806	Ultrafast Acoustic Gating of Photocurrent in Nanodevices With a Quantum Well. AIP Conference Proceedings, 2011, , .	0.3	0
807	Microwave power generation by magnetic superlattices. Applied Physics Letters, 2011, 99, 242107.	1.5	0
808	Wetting-layer-pumped continuous-wave surface emitting quantum dot laser. Proceedings of SPIE, 2012, , .	0.8	0
809	Effect of epitaxial layer thickness on the deep level defects in MBE grown $\text{Al}_{0.33}\text{Ga}_{0.67}\text{As}$ . Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 1643-1646.	0.8	0
810	In-situ electrical characterisation of a photodiode during nano-structuring with a focussed ion beam. Applied Physics A: Materials Science and Processing, 2013, 110, 935-941.	1.1	0

#	ARTICLE	IF	CITATIONS
811	Suppression of electron magnetotunneling between parallel two-dimensional GaAs/InAs electron systems by the correlation interaction. <i>Semiconductors</i> , 2013, 47, 1215-1218.	0.2	0
812	Preface: Seventh International Conference on Low-Dimensional Structures and Devices. , 2014, , .		0
813	Effects of Be acceptors on the spin polarization of carriers in p-i-n resonant tunneling diodes. <i>Journal of Applied Physics</i> , 2014, 116, 054506.	1.1	0
814	Numerical simulation of the response of substrate traps to a voltage applied to the gate of a gallium arsenide field effect transistor. <i>Materials Science in Semiconductor Processing</i> , 2014, 24, 34-39.	1.9	0
815	Detection of anomalous Hall voltages in ultrahigh-mobility two-dimensional hole gases generated by optical spin orientation. <i>Physical Review B</i> , 2015, 91, .	1.1	0
816	Nanometre scale 3D nanomechanical imaging of semiconductor structures from few nm to sub-micrometre depths. , 2015, , .		0
817	Hole spin injection from a GaMnAs layer into GaAs/AlAs/InGaAs resonant tunneling diodes. <i>Journal Physics D: Applied Physics</i> , 2016, 49, 165104.	1.3	0
818	Structural Stabilities and Elastic Thermodynamic Properties of SrTe Compound and SrTe <sub>1-x</sub> Ca <sub>x</sub> Alloy Under High Pressure. <i>Journal of Electronic Materials</i> , 2017, 46, 766-774.	1.0	0
819	Voltage- and Light-Controlled Spin Properties of a Two-Dimensional Hole Gas in p-Type GaAs/AlAs Resonant Tunneling Diodes. <i>Journal of Electronic Materials</i> , 2018, 47, 1780-1785.	1.0	0
820	Structural and optical properties of n-type and p-type GaAs <sub>(1-x)</sub> Bi <sub>x</sub> thin films grown by molecular beam epitaxy on (311)B GaAs substrates. <i>Semiconductor Science and Technology</i> , 2021, 36, 075018.	1.0	0
821	The magnetoresistance of a two-dimensional electron gas in the presence of a spatially random magnetic field. <i>Springer Proceedings in Physics</i> , 2001, , 747-748.	0.1	0
822	Combined S- and Z-shaped current bistability induced by charging of quantum dots. <i>Springer Proceedings in Physics</i> , 2001, , 773-774.	0.1	0
823	Nature of the localized phase in a two-dimensional electron system. <i>Springer Proceedings in Physics</i> , 2001, , 857-858.	0.1	0
824	Chaotic Quantum Transport in Superlattices. <i>Springer Proceedings in Physics</i> , 2001, , 745-746.	0.1	0
825	Quantum States of Self-Assembled InAs Dots Probed by Magneto-Tunneling Spectroscopy. <i>Acta Physica Polonica A</i> , 2001, 100, 165-173.	0.2	0
826	SELF-ASSEMBLED QUANTUM DOTS: STRUCTURAL AND OPTICAL PROPERTIES, AND DEVICE APPLICATIONS. , 2004, , .		0
827	BREAKDOWN OF THE QUANTUM HALL EFFECTS IN HOLE SYSTEMS AT HIGH INDUCED CURRENTS. , 2005, , .		0
828	FURTHER EVIDENCE FOR A COLLAPSE OF THE EXCHANGE-ENHANCED SPIN SPLITTING IN TWO DIMENSIONAL SYSTEMS. , 2005, , .		0



#	ARTICLE	IF	CITATIONS
829	Stochastic Carrier Dynamics in Semiconductor Superlattices. Acta Physica Polonica A, 2006, 109, 43-52.	0.2	0
830	Sharp Electroluminescence Lines Excited by Tunneling Injection Into a Large Ensemble of Quantum Dots. AIP Conference Proceedings, 2007, , .	0.3	0
831	Time Resolved Magnetophotoluminescence of Biased GaAs/AlGaAs Double Quantum Well Structure. Acta Physica Polonica A, 2008, 114, 1369-1374.	0.2	0
832	Equilibrium and Nonequilibrium Response in Nanoelectronic Structures. , 1989, , 219-315.		0
833	Resonant Tunnelling Devices in a Quantising Magnetic Field. Springer Series in Solid-state Sciences, 1989, , 324-334.	0.3	0
834	Magnetotunnelling Spectroscopy to Measure the Electron and Hole $\hat{\mu}(k)$ Dispersion Curves in the Quantum Well of Resonant Tunnelling Structures. Springer Series in Solid-state Sciences, 1992, , 645-655.	0.3	0
835	OPTICAL INVESTIGATIONS OF VERTICAL TRANSPORT IN DOUBLE BARRIER RESONANT TUNNELING STRUCTURES. , 1992, , 445-454.		0
836	Quantum Dot Fabrication by Optical Lithography and Selective Etching. , 1993, , 191-197.		0
837	Resonant Tunnelling via the Bound States of Shallow Donors. , 1993, , 83-88.		0
838	The Thermoelectric Behaviour of two Dimensional Electron and Hole Gases and Quantum Point Contacts. , 1994, , 219-232.		0
839	Tunneling Spectroscopy as a Probe of Hot Electrons in the Upper Landau Level of a 2DEG. , 1996, , 513-516.		0
840	Accurate Modeling of Double Barrier Resonant Tunneling Diodes. , 1996, , 269-290.		0
841	Cyclotron Resonance Observation of Heavy and Light Spin Subbands in an Ultra-High Mobility 2D Hole Gas in GaAs/(Al,Ga)As: Evidence for Coupled Magnetoplasmons and Many Body Effects. , 1996, , 539-542.		0
842	Molecular Beam Epitaxy: Physics and Technology. , 1998, , 11-24.		0
843	Vortex Lattice Melting in Bi2Sr2CaCu2O8+ $\hat{\nu}$ Single Crystals; Insights from Scanning Hall Probe Microscopy. , 1998, , 401-406.		0
844	SELF-ASSEMBLY OF InAs/GaAs QUANTUM DOTS: SUBSTRATE ORIENTATION EFFECTS. , 1999, , .		0
845	Decay of coherent acoustic phonons generated by femtosecond pulsed optical excitation and injected in a Wannier-Stark superlattice (Conference Presentation). , 2017, , .		0
846	Transformation of polarons into magnetopolarons in GaAs quantum well. Physica E: Low-Dimensional Systems and Nanostructures, 2021, 136, 115019.	1.3	0